

EXHIBIT A

U.S. SERIAL NO.: 10/521,619

ASSIGNMENT OF PATENTS

This Assignment of Patents (this "Assignment") is effective as of the Initial Closing Date (as defined in the Asset Purchase Agreement (the "Asset Purchase Agreement"), dated as of October 10, 2003, by and among ASML Holding N.V., a Dutch company ("Parent"), ASML U.S., Inc., a Delaware corporation and a wholly-owned subsidiary of Parent ("Seller U.S."), and the other affiliates of Seller U.S. party thereto (together with all of the foregoing parties, each a "Seller" and collectively the "Sellers"), on the one hand, and Thermal Acquisition Corp., a Delaware corporation ("Buyer"). Capitalized terms used herein but not defined shall have the meanings ascribed to such terms in the Asset Purchase Agreement.

WHEREAS, upon the terms and subject to the conditions in the Asset Purchase Agreement, Sellers have agreed to assign and transfer to Buyer, among other things, certain Patents (as defined below);

WHEREAS, in order to further effect the assignment and transfer of such Patents, Buyer has requested that Seller U.S. execute and deliver to Buyer this Assignment;

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged:

1. Sellers agree to and hereby do assign, sell, transfer, grant and convey to Buyer, its successors and assigns, all of Sellers' worldwide right, title and interest in and to all Patents listed on schedule 3.18(a)(i) of the Disclosure Schedule and all causes of action, demands, judgments, claims, or other similar rights of Sellers relating primarily to such Patents.

"Patents" shall mean all U.S. and foreign patents and applications therefor and all reissues, divisions, renewals, extensions, provisionals, continuations and continuations-in-part thereof.

2. Sellers authorize and request the United States Patent and Trademark Office and head of any foreign patent office to issue all patent registrations which may issue on any applications for any Patents to Buyer, its successors and assigns, in accordance with this Assignment.

3. Promptly upon the request of Buyer, Sellers shall execute such documents and perform such actions as may be necessary to perfect the assignment of rights contained in this Assignment.

4. Nothing herein shall affect, or be deemed to affect, the representations, warranties, covenants, and indemnities contained in the Asset Purchase Agreement.

5. This Assignment may be executed in one or more counterparts and signature may be delivered by facsimile, each of which shall be deemed an original, but all of which together shall constitute one and the same instrument.

IN WITNESS WHEREOF, Seller U.S. has caused this instrument to be executed by its
duly authorized corporate officer as of the Closing Date:

ASML U.S., Inc.

By:

C. Douglas Marsh

Name: C. Douglas Marsh

Title: Vice President Business Integration
& U.S. Institutional Relations

ACKNOWLEDGED AND AGREED:

Thermal Acquisition Corp., a Delaware Corporation

By:

Jerauld Cutini

Name: Jerauld Cutini
Title: President and Chief Executive Officer

IN WITNESS WHEREOF, Seller U.S. has caused this instrument to be executed by its
duly authorized corporate officer as of the Closing Date.

ASML U.S., Inc.

By:

Name: C. Douglas Marsh
Title: Vice President Business Integration
& U.S. Institutional Relations

ACKNOWLEDGED AND AGREED:

Thermal Acquisition Corp., a Delaware Corporation

By:


Name: Jerauld Cutini
Title: President and Chief Executive Officer

DISCLOSURE SCHEDULES

SCHEDULE 3.18(a)(i)

The following Patents:

Attachment 1 to
Disclosure Schedule 3.18(a)(1)

Reference No.			Title/Inventor	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	16178 6	AJT	LOW TEMPERATURE CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE FILMS	07/063,727 06/29/87	4,845,054 07/04/89	
FA	16178 6-JP	AJT	LOW TEMPERATURE CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE FILMS	61-137340 06/14/86	2134184 12/26/87	Japan
A	16178 7	AJT	CVD REACTOR AND GAS INJECTION SYSTEM	07/044,326	4,834,022	
FA	16178 7-JP	AJT	CVD REACTOR AND GAS INJECTION SYSTEM	10/27/87 05/30/89	2076448 08/09/96	Japan
A	16178 8	AJT	FLUIDIZED BED HEATER FOR SEMICONDUCTOR PROCESSING	07/14/86 03/01/85	4,673,799 06/16/87	
A	40356	AJT	RAPID INFRARED CURING OF PHENOL-PHENOLIC, EPOXY AND OTHER RESINS/ALLEY, Kunita, et al.	707262	4,834,020 05/30/89	
A	44048	AJT	ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION APPARATUS AND METHOD/ Bartholomew	07/128,806 12/04/87	4,834,020 05/30/89	
FA	44048 JP	AJT	ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION APPARATUS AND METHOD/ Bartholomew	63-307633 12/05/88	2930960 05/21/99	Japan
FA	44048 KR	AJT	ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION APPARATUS AND METHOD/ Bartholomew	Closed		South Korea
A	44153	AJT	INDUSTRIAL ROBOT FOR USE IN CLEAN ROOM/ Stevens	07/089,591 08/26/87	4,787,813, 11/29/88 Abandoned	Expired
A	44521	AJT	METHOD FOR IMPROVING STEP COVERAGE OF DIELECTRIC IN VLSI CIRCUITS/Shamshoian	06/907,503 09/15/86	Abandoned	
A	44521 1	AJT	METHOD FOR IMPROVING THE STEP COVERAGE OF DIELECTRIC IN VLSI CIRCUITS/Shamshoian	07/214,909 06/29/88	4,891,247 01/02/90	Abandoned

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10/01/26

10/8/2003

Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 44521 1-JP AJT	BOROSILICATE GLASS FILMS FOR MULTILEVEL METALLIZATION STRUCTURES IN SEMICONDUCTOR DEVICES AND METHOD				62-23191 09/16/87	Abandoned	Japan
FE 44521 1-EP AJT	METHOD FOR IMPROVING THE STEP COVERAGE OF DIELECTRIC IN VLSI CIRCUITS						
A 47444 AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYED SILANE/Graefeld	Closed					Europe
FA 47444 DE AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/ Graefeld	07/238,826 08/31/88	07/798,829 (A-47444-1)	Abandoned in favor			
FA 47444 KR AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/ Graefeld	08/30/89		Abandoned		Germany	
FA 47444 JP AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/ Graefeld	12/472/89 08/31/89		Abandoned		South Korea	
FA 47444 GB AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/ Graefeld	01-226366 08/31/89		Abandoned		Japan	
FA 47444 EP AJT MSS	PROCESSES USING DISILANE/Graefeld	8919291.8 08/24/89	2222416/ 03/03/93	Abandoned		United Kingdom	
FE 47444 EP AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYED SILANE/Graefeld	Closed				Europe	
FP 47444 PC AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYED SILANE/Graefeld	Closed				PCT	
A 47444 1 AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/ Graefeld	07/798,829 11/22/91	07/991,500 12/17/92	Abandoned in favor of 07/991,500 (A-47444-2)			
A 47444 2 AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/ Graefeld	07/991,500 10/27/94	08/329,772	Abandoned in favor of 08/329,772 (A-47444-3)			
A 47444 3 AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/ Graefeld	07/570,122 08/17/90		Abandoned per client Nr 09/1498			
A 52244 AJT	ELECTRICALLY INSULATED PIPE COUPLING APPARATUS/Graefeld						
A 52353 AJT WSG	INJECTOR AND METHOD FOR DELIVERING GASEOUS CHEMICALS TO A SURFACE/Bartolomew	07/542,243 06/21/90	5,088,773 02/18/92				
A 52354 AJT	SELF CLEANING ORIFICE/Kamim	07/513,807	5,126,975 08/11/92				
			5,113,789				

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Reference No.	Title/Invention				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 52354 KR	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	042490	03/19/92		
FA 52354 JP	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	1470890	188614 01/13/99		South Korea
FA 52354 TW	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	2-216835 08/17/90	297490 09/03/99		Japan
FB 52354 DE	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	79106834 08/15/90	51810 02/14/92		Taiwan
FB 52354 ES	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/05/90	69017008 02/15/95		Germany
FB 52354 FR	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307393.9 07/06/90	453679 02/15/95		Spain
FB 52354 GB	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/06/90	453679 02/15/95		France
FB 52354 GR	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/06/90	453679 02/15/95		United Kingdom
FB 52354 IT	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/06/90	453679 02/15/95		Greece
FB 52354 BE	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/06/90	453679 02/15/95		Italy
FB 52354 CH	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/06/90	453679 02/15/95		Belgium
FB 52354 EP	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/06/90	453679 02/15/95		Switzerland
FB 52354 LU	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/06/90	453679 02/15/95		Europe
FB 52354 NL	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/06/90	453679 02/15/95		Luxembourg
FB 52354 SE	WSG	ATJ	SELF CLEANING FLOW CONTROL OFFICE/Kamian	90307398.9 07/06/90	453679 02/15/95		Netherlands
							Sweden

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1089128

10/8/2003

Reference No.				Title/Invention		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FB	52354	DK	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian		90307398.9 07/06/90	453679 02/15/95 Abandoned	Denmark
FR	52354	AT	AJT	SHIP CLEANING FLOW CONTROL ORIFICE/Kamian		90307398.9 07/06/90	453679 02/15/95 Abandoned	Austria
A	53835	AJT JEM		U-SHAPED HEATER LINES/Walker		07/601,261 10/22/90	08/19/92 Abandoned	
FA	53835	KR	AJT	U-SHAPED HEATER LINES/Walker		18591/91 10/22/91	08/19/92 Abandoned	South Korea
FA	53835	JP	AJT	U-SHAPED HEATER LINES/Walker		3-274072 10/22/91	08/19/92 Abandoned	Japan
FB	53835	EP	AJT	HEATED FLUID SUPPLY LINE/Walker		91309735.8 10/22/91	08/19/92 Abandoned	Europe
A	53836	AJT		LIQUID SOURCE BUBBLER/Richie		07/601,270 10/22/90	5,073,922 01/07/92	
FA	53836	JP	AJT	LIQUID SOURCE BUBBLER/Richie		3-274069 10/22/91	1929857 05/12/95	Japan
FA	53836	KR	AJT MSS	LIQUID SOURCE BUBBLER/Richie		18592/91 10/22/91	191851 01/27/99	South Korea
FB	53836	EP	AJT	LIQUID SOURCE BUBBLER/Richie		91309736.6 10/22/91	Abandoned	Europe
A	53837	AJT		X-RAY TUBE INCLUDING FLUID X-RAY SOURCE/Galbraith	Closed			
A	53839	AJT		LIQUID LEVEL SENSOR ASSEMBLY/Goodrich		07/601,408 10/23/90	5,029,471 07/09/91	
FA	53839	JP	AJT	LIQUID LEVEL SENSOR ASSEMBLY/Goodrich		3-275317 10/23/91	1905072 02/08/95	Japan
FA	53839	KR	AJT MSS	LIQUID LEVEL SENSOR ASSEMBLY/Goodrich		18633.91 10/23/91	216658 06/01/99	South Korea
FB	53839	EP	AJT	LIQUID LEVEL SENSOR ASSEMBLY/Goodrich		91309743.2 10/22/91	Abandoned	Europe

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Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 53860	AT	VAPOR DELIVERY SYSTEM	Closed			
A 53861	AT	CHMICAL REFILL SYSTEM	Closed			
A 56598	AT	HEATER FOR PROCESSING GASES/Collins	07/971,490 11/04/92	1,377,300 12/27/94		
FA 56598	JP	AT	GAS HEATER FOR PROCESSING GASES/Collins	6-511396 11/03/93	Abandoned	Japan
FA 56598	KR	AT	GAS HEATER FOR PROCESSING GASES/Collins	70179095 11/03/93	163256 09/04/98	South Korea
FR 56598	EP	AT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	0666972 01/07/99	Europe
FR 56598	HK	AT	GAS HEATER FOR PROCESSING GASES/Collins	98114622.0 12/22/98	101-42063 05/16/00	Hong Kong
FR 56598	DE	AT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	P69322975 01/07/99	Germany
FR 56598	FR	AT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	0666972 01/07/99	France
FR 56598	GB	AT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	0666972 01/07/99	Great Britain
FR 56598	IT	AT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	0666972 01/07/99	Italy
FP 56598	PC	AT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	0666972 01/07/99	
A 57727	AT	BPSSG STABILITY ENHANCING CAP LAYER/ Bogdan	PCT/US93/10532 11/03/93	Closed	PCT	
A 57728	AT	OZONE PRETREATMENT FOR IMPROVED VIA RESISTANCE/Curtis	Closed			
A 58019	AT	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE USING HEKAMETHYLDISILAZANE/Kressell	08/071,516 06/03/93	5,304,398 04/19/94		
FP 58019	PC	AT	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE FROM HEKAMETHYLDISILAZANE AND OZONE/OXYGEN/Kressell		Abandoned	PCT

Reference No.		Title/Inventor	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	59071	AJT	A THIN FILM SEMICONDUCTOR DEVICE AND METHOD/Harada	08/191,091 02/03/94	Abandoned
FP	59071	PC	AJT A THIN FILM SEMICONDUCTOR DEVICE AND METHOD/Harada	PCT/US94/01352 02/04/94	Abandoned
A	59072	AJT	METHOD OF MANUFACTURING A GLASS SUBSTRATE FOR A THIN FILM/Harada	08/191,093 02/03/94	Abandoned in favor of FWC 08/542,279 (A-59072-1)
FP	59072	PC	AJT METHOD OF MANUFACTURING A GLASS SUBSTRATE FOR A THIN FILM/Harada	PCT/US94/01278 02/04/94	Abandoned
A	59072	1	AJT METHOD OF MANUFACTURING A GLASS SUBSTRATE FOR A THIN FILM/Harada	08/542,279 10/12/95	Abandoned
A	59073	AJT MSS	METHOD OF MANUFACTURING SIDE WALLS AND SEMICONDUCTOR DEVICE HAVING SIDE WALLS/Harada, Hatano	08/237,691 05/04/94	Abandoned in favor of FWC 08/512,346 (A-59073-1)
FP	59073	PC	AJT MSS SEMICONDUCTOR WITH SIDE WALLS/Harada, Hatano	PCT/US94/05315 05/13/94	Abandoned
A	59073	1	AJT MSS SEMICONDUCTOR DEVICE HAVING SIDE WALLS/Harada, Hatano	08/512,346/ 08/08/95 FWC of 08/237,691 Filed 05/04/94	Abandon
A	59425	AJT	TRIETHOXYSTILANE (TRIES) AS A PRECURSOR FOR THE DEPOSITION OF SiO ₂ /Schmitt	Closed	
A	59471	AJT MSS	SINGLE BODY INJECTOR AND METHOD FOR DELIVERING GASES TO A SURFACE/Dedonney	08/276,815 07/18/94	
PA	59471	JP	AJT MSS TO A SURFACE/Dedonney	7-181702. 07/18/95	Abandoned in favor of FWC 08/621,772 (A-59471-1)
PA	59471	KR	AJT MSS TO A SURFACE/Dedonney	2790437 06/12/98	Japan
PA	59471	TW	AJT MSS TO A SURFACE/Dedonney	190335 01/20/99	South Korea
FB	59471	DE	AJT MSS TO A SURFACE/Dedonney	106107 12/29/99	Taiwan
					Germany

I-7935/MSS (463035-22)
10/01/08

Reference No.	Title/Invention				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FB 59471 EP	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedomney	MSS	95304783.4	0697376 07/10/95	11/03/99	Europe
FB 59471 FR	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedomney	MSS	95304783.4	0697376 07/10/95	11/03/99	France
FB 59471 GB	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedomney	MSS	95304783.4	0697376 07/10/95	11/03/99	Great Britain
FB 59471 HK	AJT	SINGLE BODY INJECTOR	MSS	98111870.5	10110108 11/09/98	06/16/00	Hong Kong
FB 59471 IT	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedomney	MSS	95304783.4	0697376 07/10/95	11/03/99	Abandoned
FB 59471 NL	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedomney	MSS	95304783.4	0697376 07/10/95	11/03/99	Italy
A 59471 1	AJT	SINGLE BODY INJECTOR AND METHOD FOR DELIVERING GASES TO A SURFACE/Dedomney, Graham, Miller	MSS	08/621,772 03/22/96 FWC of 08/276,815 Filed 07/18/94	5,683,516 11/03/99 11/04/97		Netherlands
A 59471 2	AJT	METHOD OF MANUFACTURING AN INJECTOR FOR CHEMICAL VAPOR DEPOSITION PROCESSING/Dedomney, Gralnick, Miller	MSS	08/869,485 06/04/97. Div. of 08/276,815 Filed 07/18/94	5,935,647 08/10/99		
A 59471 3	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Miller, Dobkin	MSS	08/892,469 07/14/97 CIP of 08/621,772; which is an FWC of 08/276,815	6,022,414 02/08/00		
FA 59471 3-TW	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Miller, Dobkin	MSS	87111447 07/14/98	124167 04/24/01		Taiwan
A 59471 4	AJT	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, Dobkin	MSS SMF	09/113,823 07/10/98 CIP of 08/892,469; 08/621,772; which is an FWC of	6,200,389 03/13/01		

Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FP	59471 4-PC	AJT	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	08/276,815 07/10/98	PCT/US98/14393 07/10/98	PCT
FA	59471 4-CN	AJT	MSS SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	98207203.3 07/10/98		China
FA	59471 4-HK	AJT	MSS SINGLE BODY INJECTOR AND DEPOSITION CHAMBER; Adam Q. Miller, Daniel M. Dobbin	00108287.5 12/21/00		
FA	59471 4-JP	AJT	MSS SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	2000-503260 07/10/98		Japan
FA	59471 4-KR	AJT	MSS SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	2000-700430 07/10/98	355068 09/29/02	South Korea
FA	59471 4-SG	AJT	MSS SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	9906104-6 07/10/98	88697 03/04/02	Singapore
FE	59471 4-EP	AJT	MSS SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	98933329.9 07/10/98		Europe
A	59471 5	AJT	MSS SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, Dobbin SMF	09/757,542 01/09/01 Divisional of: 09/113,823 07/10/98	6,521,048 02/18/03	
A	60164	AJT	METHOD OF FORMING A PLANAR LAYER OF MATERIAL/ty, Lightfoot, Lamond	08447,809 05/23/95	5,668,063 09/16/97	
FA	60164 KR	AJT	METHOD OF PLANARIZING A LAYER OF MATERIAL/ty, Lightfoot, Lamond	708269/97 05/06/96		South Korea
FA	60164 JP	AJT	METHOD OF PLANARIZING A LAYER OF MATERIAL/ty, Lightfoot, Lamond	05/06/96		
FB	60164 HP	AJT	METHOD OF PLANARIZING A LAYER OF MATERIAL/ty, Lightfoot, Lamond	05/06/96		Japan
FP	60164 PC	AJT	METHOD OF PLANARIZING A LAYER OF MATERIAL/ty, Lightfoot, Lamond	05/06/96		Europe
A	62201	AJT	MSS STRESS RELIEF OF APCVD OXIDE FILMS/FY	PCT/US96/06375 05/06/96	Closed 08/27/96	PCT
A	62732	AJT	NITROGEN SHIELD/Vn Thm	08/704,227 08/28/96	5,786,278 07/22/98	
				08/800,106	Abandoned in favor of FWC 08/976,928	

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10/8/2003

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 62732 1	JEM	AJT	PROTECTIVE GAS SHIELD FOR CHEMICAL VAPOR DEPOSITION APPARATUS	02/13/97 08/07/96, 928 11/24/97	(A-62732-1) 5,944,900 08/31/99	
A 62732 2	JEM	AJT	PROTECTIVE GAS SHIELD FOR CHEMICAL VAPOR DEPOSITION APPARATUS			
A 62786	JEM	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	Closed		
A 62786 1	MSS	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	08/573,318 12/15/95	08/599,092 08/25/99 (A-62786-1)	Abandoned in favor of 08/599,092 (A-62786-1)
FA 62786 1-CN	AJT	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	02/07/96 CIP. of 08/573,318 Filed 12/15/95		
FA 62786 1-JP	AJT	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	96198872,X 12/11/96		China
FA 62786 1-KR	AJT	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	9-522910 12/11/96		Japan
FA 62786 1-SG	AJT	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	704363/98 12/11/96		South Korea
RA 62786 1-TW	AJT	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	9802389-8 12/11/96	51957 08/22/00	Singapore
RE 62786 1-EP	AJT	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	85109526 08/06/96 12/13/97	088844	Taiwan
RE 62786 1-HK	AJT	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	96943723,5 12/11/96		Europe
EP 62786 1-PC	AJT	AJT	METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION/Carvalheira	99100518,5 02/08/99		
A 62998	AJT	AJT	DIELECTRIC PLANARIZATION TECHNIQUE WITH IMPROVED RELIABILITY/Batin	PCT/US96/19819 12/11/96	Closed	Hong Kong
A 63007	AJT	JEM	METHOD OF IMPROVING & DEPOSITION THICKNESS CONTROL IN AN APCVD REACTOR/Yem		Closed	PCT
A 63008	AJT	AJT	OPTIMIZING OF SiCO ₂ FILM CONFORMALITY IN ATMOSPHERIC PRESSURE CHEMICAL VAPOR	02/801,997	5,855,957	

I-71935/MSS (463035-328)
1099178

Reference No.	Title/Invention				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 63008 TW	JEM	DEPOSITION			02/18/97	01/03/99	
FP 63008 PC	AJT	OPTIMIZING SiO ₂ FILM CONFORMALITY IN TiO ₂ /Si APCVD			02/18/98	107673 02/02/00	Taiwan
A 63265	AJT	OPTIMIZATION OF SiO ₂ FILM CONFORMALITY IN ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION			PCT/US98/02842 02/17/98	Abandoned.	PCT
FP 63265 PC	JEM	LOW K DIELECTRICS PREPARED FROM CROSS-LINKED PPX _x (CL-PPX _x)/Lo _y			08/679,864 07/16/96	5,925,420 07/20/99	
A 63347	AJT	CROSSLINKED AROMATIC POLYMERS AS LOW k DIELECTRIC/Lo _y			PCT/US97/10575 07/14/97	Abandoned.	PCT
A 63579	AJT	A METHOD OF PLANARIZING A DIELECTRIC LAYER WITH REDUCED HYDROGEN DIFFUSION/ Baking			Closed		
A 63660	AJT	LOW k DIELECTRICS PREPARED FROM PECVD AND PECVD OF SELECTED SILOKANES/Lo _y			Hold		
A 63661	AJT	METHOD FOR FORMING VERTICALLY EXTENDED EMBEDDED LOW k MATERIALS/Py			09/019,349 02/05/98	5,976,258 11/02/99	
A 63662	AJT	OPTIMIZATION OF SiO ₂ FILM CONFORMITY			Closed		
A 63665	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bally, Brady			08/823,635 03/11/97	5,916,378 06/29/99	
FA 63665 CN	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bally, Brady			98804123,5 03/06/98		China
FA 63665 HK	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bally, Brady			00106069,3 09/26/00	Abandoned	Hong Kong
FA 63665 JP	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bally, Brady			10-539667 03/10/98		Japan
FA 63665 KR	AJT	METHOD OF CONTAMINATION REDUCTION BY			99-7008224		South Korea

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Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 63665 SG	MSS	AJT	FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady		03/06/98	9904262-4 03/06/98	67703 10/24/00
FA 63665 TW	MSS	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady				Singapore
FE 63665 EP	MSS	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady				Taiwan
FP 63665 PC	MSS	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady				Europe
A 63669 PC	MSS	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady				PCT
A 63669 FC	MSS	AJT	FLANGE CLAMP/Mateos, Kamian				PCT
A 63672 JEM	JEM	AJT	LINEAR INJECTOR WITH VACUUM COMPATIBILITY/McCullagh, Labossi, Herman, Ellul		03/06/98 11/06/97	08/746,608 11/13/96	Abandoned
A 63673 JEM	JEM	AJT	DIRECT DRIVE ROTATIONAL MOTOR WITH AXIAL VACUUM/McCullagh				PCT
A 63674 MSS	MSS	AJT	INJECTION SEAL Miller, Veek				Closed
A 63675 JEM	JEM	AJT	EXHAUST VENT ASSEMBLY FOR CHEMICAL VAPOUR DEPOSITION SYSTEMS/McCullagh				Closed
A 63676 JEM	JEM	AJT	THERMAL CONDITIONING TOWER/Kline		08/038,882 04/14/97	5,938,851 08/17/99	
A 63677 MSS	MSS	AJT	MONOBLOK INJECTION MODIFICATION/McCullagh		09/019,342 02/05/98		Abandoned
A 64309 MSS	MSS	AJT	NITRIC OXIDE COMPOUND CONDENSER/Garcia				
A 64725	AJT	AJT	NITROGEN DILUENT GAS FREE OPERATION OF CONDENSER			59471-3 and closed	Combined with A-59471-3 and closed

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Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 64873	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR GENERATORS/Grenade			
A 64873 1	MSS	AJT	APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	09/018,021 02/02/98	6,026,589 02/22/00	
PA 64873 CA	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	09/457,929 12/08/99 Div. of 09/018,021 02/02/98		
PA 64873 CN	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	2319636 02/01/99	Abandoned	Canada
PA 64873 HK	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	99802634-4 02/01/99		China
PA 64873 IL	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	01104936-8 07/16/01	Abandoned	Hong Kong
PA 64873 JP	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	137533 02/01/99	Abandoned	Israel
PA 64873 KR	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	2000-529567 02/01/99		Japan
PA 64873 SG	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	2000-7008430 02/01/99	376643 03/06/03	South Korea
PA 64873 TW	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	200004218-2 02/01/99	74927 08/30/02	Singapore
PE 64873 EP	MSS	AJT	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	88100719 01/18/99	122455 03/16/01	Taiwan
				999033366 02/01/99		Europe

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Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries	
	EP	64873	PC	AJT	WAFER CARRIER/Yeo, Bailey	PCT/US99/02100 02/01/99	Closed	PCT
A	63383	AJT	JEM	MSS	FREE FLOATING SHIELD/DeDomney, et al.	09/008,024 01/16/98	1,849,088 12/15/98	
A	63383	1	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	09/185,180 11/03/98	6,056,824 05/02/00	
EP	63383	1-PC	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	PCT/US98/25740 12/04/98	Closed	PCT
FA	63383	1-CA	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2318147 12/04/98		Canada
FA	63383	1-CN	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	988126414 12/04/98		China
FA	63383	1-HK	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Christopher A. Peabody, Jay B. DeDomney, Lawrence D. Bartholomew	01104322.0 06/21/01	Abandoned	Hong Kong
EP	63383	1-EP	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	98960728.3 12/04/98		Europe
FA	63383	1-IL	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	137315 12/04/98	Abandoned	Israel
FA	63383	1-JP	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2000-540285 12/04/98	3416114 04/04/03	Japan
FA	63383	1-KR	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2000-7007859 12/04/98	346767 07/18/02	South Korea
FA	63383	1-SG	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	87119638 11/26/98	74790 09/30/02	Singapore
A	63383	1-TW	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	200003932-1 12/04/98	133711 10/27/01	Taiwan
FA	63383	2	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	09/492,420 01/27/00	6,352,592 BI 03/05/02	
FA	63383	2-CA	AJT	MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2304548 04/07/00	Abandoned	Canada

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Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No/ Issue Date	Foreign Countries
PA 65583 2-CN AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.			00106454.1 04/10/00		China
PR 65583 2-EP AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.			00302953.5 04/07/00		Europe
PA 65583 2-HK AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.			02012663 02/21/02	Abandoned	Hong Kong
PA 65583 2-JP AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.			2000-108638 04/10/00		Japan
PA 65583 2-KR AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.			2000-0018645 04/10/00	338891 05/20/02	South Korea
PA 65583 2-MY AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.			P20001457 04/07/00		Malaysia
PA 65583 2-SG AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.			200001878.8 03/31/00		Singapore
PA 65583 2-TW AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.			89106510 04/08/00		Taiwan
A 65816 CA AJT MSS	CYCLOPHANE DERIVATIVES CONTAINING CROSS-LINKING GROUPS/Golden			056644 04/03/00	Abandoned	Thailand
A 65965 AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING Rose; Loper; Felt			091067704. 04/28/98	6,068,884 05/30/00	
PA 65965 CA AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING Rose; Loper; Felt			2,330,040 04/15/99	Abandoned	Canada
PA 65965 CN AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING Rose; Loper; Felt			998065064 04/15/99		China
PA 65965 HK AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING Rose; Loper; Felt			0110834.0 11/15/01	Abandoned	Hong Kong
PA 65965 IL AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING Rose; Loper; Felt			139128 04/15/99	Abandoned	Israel

Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	65965	JP	AJT MSS	Lopata; Feltz LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Feltz	2000-545704 04/15/99	Japan
FA	65965	KR	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Feltz	2000-7012019 04/15/99	South Korea
FA	65965	SG	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Feltz	20000399948 04/15/99	Singapore
FA	65965	TW	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Feltz	88106331 04/28/99	Taiwan
EE	65965	EP	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Feltz	999175292 04/15/99	Europe
EP	65965	PC	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Feltz	PC10US99/08246 04/15/99	Closed
A	65965 -1		AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Feltz	09/361,667 07/27/99	PCT
A	65965 -2		AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Feltz	10/637,913 08/08/03	
EA	66484		AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR DELIVERING GASOUS CHEMICALS AND METHOD/Daehan; Stifter; McGrogan	09/113,730 07/10/98	Abandoned
EA	66484	TW	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR DELIVERING GASOUS CHEMICALS AND METHOD/Daehan; Stifter; McGrogan	88110478 06/22/99	Taiwan
FP	66484	PC	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR	PCT10US99/08702 04/21/99	PCT

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Reference No.	The Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P 66959	AJT	DELIVERING GASEOUS CHEMICALS AND METHOD/Debtier, Stifter; McGregor				
	MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew, Bailey; Ewald; Boland.		60/118,286 02/02/99	Closed	
A 66959	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew, Bailey; Ewald; Boland.		09/493,492 01/28/00	6,143,680 11/07/00	
RA 66959	CA	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew, Bailey; Ewald; Boland.	2362694 02/01/00	Abandoned	Canada
FA 66959	CN	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew, Bailey; Ewald; Boland.	00804644.1 02/01/00		China
FA 66959	HK	MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew, Bailey; Ewald; Boland.	02104112.3 05/31/02	Abandoned	Hong Kong
FA 66959	IL	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	144696 02/01/00	Abandoned	Israel
FA 66959	JP	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	2000-599919 02/01/00		Japan
FA 66959	KR	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	2001-7009763 02/01/00		South Korea
FA 66959	SG	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	200104725-7 02/01/00		Singapore
FA 66959	TW	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew, Bailey; Ewald; Boland	89101846 02/02/00		Taiwan
EP 66959	EP	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew, Bailey; Ewald; Boland	00910443.8 02/21/00		Europe
EP 66959	PC	AJT	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew, Bailey; Ewald; Boland	US000102606 02/01/00	Closed	PCT

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Reference No.	Title/Inventor			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 66959 1	AJT	WAFFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Roland;			Closed	
P 67178	AJT	GAS DELIVERY METERING TUBE/Stoddard; Yao; Hamilton; Ingle; DeSai; Knutiravet; Peabody	MSS	60/135,358 05/21/99		
A 67178	AJT	GAS DELIVERY METERING TUBE/Yao; Stoddard; Yao; Hamilton; Young; DeSa	MSS	09/470,446 12/22/99		
FA 67178 CA	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	23/05758 05/18/00	Abandoned	Canada
FA 67178 CN	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	00/108583.2 05/18/00	ZL00108583.2 05/21/03	China
FB 67178 EP	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	00/04190.2 05/18/00		Europe
FA 67178 HK	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	00/102509.9 04/10/01		
FA 67178 JP	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	2000-148939 05/19/00		Hong Kong
FA 67178 KR	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	2000-0026966 05/19/00		Japan
FA 67178 MY	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	05/19/00		South Korea
FA 67178 SG	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	PI-200002163 05/17/00		Malaysia
FA 67178 TH	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	200002705-2 05/16/00		Singapore
FA 67178 TW	AJT	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MSS	05/18/00	Abandoned	Thailand
P 67178 I	MSS	GAS DELIVERY METERING TUBE/Ingle; Stoddard; Yao; Hamilton; Young; DeSa	MDV	89/06456 04/07/00	140755 01/09/02	Taiwan
A 67178 1	AJT	IMPROVED GAS DELIVERY METERING TUBE/DeDonney; DeSa	MSS	Untitled		
FA 67178 1-CN	MSS	GAS DELIVERY METERING TUBE/Anthony De; Iey	MDV	02/14/0679.0 07/12/02		China

Reference No.	The Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 67178 1-JP	MSS	GAS DELIVERY METERING TUBE/Anthony Dees; Jay B. Dedonney; Samuel Kunita	MDV.	2002-206050	07/15/02	2002-0040745	Japan
FA 67178 1-KR	MSS	GAS DELIVERY METERING TUBE/Anthony Dees; Jay B. Dedonney; Samuel Kunita	MDV.	2002-206050	07/12/02	2002-0040745	South Korea
FA 67178 1-MY	MSS	GAS DELIVERY METERING TUBE/Anthony Dees; Jay B. Dedonney; Samuel Kunita	MDV.	2002-206050	07/12/02	2002-0040745	Malaysia
FA 67178 1-SG	MSS	GAS DELIVERY METERING TUBE/Anthony Dees; Jay B. Dedonney; Samuel Kunita	MDV.	2002-206050	07/09/02	2002-0040745	Singapore
FA 67178 1-TW	MSS	GAS DELIVERY METERING TUBE/Anthony Dees; Jay B. Dedonney; Samuel Kunita	MDV.	2002-206050	07/09/02	2002-0040745	Taiwan
FB 67178 1-EP	MSS	GAS DELIVERY METERING TUBE/Dees; DeDeonney; Kunita	MDV.	0225-0062-0	07/15/02	07/370,331	Europe
A 67383	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	MSS	0225-0062-0	06/22/89	06/22/89	Abandoned
FA 67383 JP	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Makawili	165499/90.	05/22/90	2918,300	Japan
FA 67383 KR	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Makawili	1990-9257	06/22/90	162652	South Korea
FA 67383 TW	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Makawili	09/01/98	04/23/99	04/23/99	Abandoned
FB 67383 DR	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Makawili	06/22/90	06/22/90	50934-08/21/91	Taiwan
FB 67383 EP	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Makawili	90111648.3	06/20/90	0404101	Germany
FB 67383 FR	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Makawili	90111648.3	06/20/90	05/01/96	Europe
FB 67383 GB	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Makawili	0404101	05/01/96	0404101	France
FB 67383 NL	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Makawili	0404101	05/01/96	05/01/96	Great Britain
A 67383 1	AT	METHOD FOR DEPOSITING SILICON DIOXIDE	FILM AND PRODUCT/Makawili	0404101	05/01/96	0404101	Netherlands
				07/661,837	02/27/91	02/27/91	Abandoned

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 67389	ATJ MSS	ATJ MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawill	07/386,903 07/28/89	4,993,358 02/19/91	
FA 67389	JP. MSS	ATJ MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawill	201089/90 07/27/90	Abandoned	Japan
FA 67389	KR MSS	ATJ MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawill	11454/1990 07/27/90	Abandoned	South Korea
FA 67389	TW MSS	ATJ MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawill	79105355 07/29/90	47787 03/26/91 Abandoned	Taiwan
EP 67389	EP ATJ. MSS	ATJ. MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawill	90114325.3 07/26/90	Abandoned	Europe
A 67390	ATJ MSS	ATJ MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawill	07/409,125 09/19/89	5,059,770 10/22/91	
FA 67390	JP. MSS	ATJ MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawill	242205/90 09/12/90	2133364 11/14/97	Japan
FA 67390	KR MSS	ATJ MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawill	14732/90 09/18/90	160510 08/19/98	South Korea
FA 67390	TW MSS	ATJ MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawill	79105354 07/29/90	51351 01/23/92	Taiwan
EP 67390	EP ATJ MSS	ATJ MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY.Y.AND METHOD OF OPERATION/Mahawill	90115336.1 08/10/90	0418541 06/15/94	Europe
EP 67390	DE MSS	ATJ MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY.Y.AND METHOD OF OPERATION/Mahawill	90115336.1 08/10/90	0418541 06/15/94	Germany
EP 67390	FR MSS	ATJ MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY.Y.AND METHOD OF OPERATION/Mahawill	90115336.1 08/10/90	0418541 06/15/94	France
EP 67390	NL MSS	ATJ MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawill	90115336.1 08/10/90	0418541 06/15/94	Netherlands
A 67391	ATJ MSS	ATJ MSS	METHOD OF SOLDERING IN A CONTROLLED CONVECTION SURFACE-MOUNT REFLOW FURNACE/Alley, Camarsi, Daly, Roffey	07/677,661 03/29/91	5,232,145 03/03/93	Great Britain
A 67392	ATJ MSS	ATJ MSS	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TiN AND FLUORIDE DOPED INDIUM OXIDE BY	07/668,838 03/13/91	5,122,391 06/16/92	

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
	Applicant	Inventor	Co-Inventor			
PA 67392 JP	AJT MSS	APCVD/Mayer	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	5351992 03/12/92	Abandoned	Japan
PA 67392 KR	AJT MSS	APCVD/Mayer	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	4058/1992 03/12/92	Abandoned	South Korea
EP 67392 EP	AJT MSS	APCVD/Mayer	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	92003329-6 02/27/92	Abandoned	Europe
A 67392 1	AJT MSS	APCVD/Mayer	METHOD AND APPARATUS FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	07/856,457 03/24/92	Abandoned	
P 67388	AJT MSS	Yuh	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	60/135,362 05/21/99	Closed	
A 67388	AJT MSS	Yuh	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	09/574,826 05/19/00	6,576,060 06/10/03	China
PA 67388 CN	AJT MSS	Yuh	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	09807884-X 05/19/00		
FA 67388 JP	AJT MSS	Stoddard, Yuh	PROTECTIVE GAS SHIELD APPARATUS/Neil; Stoddard, Yuh	2000-620151 05/19/00		Japan
FA 67388 KR	AJT MSS	Stoddard, Yuh	PROTECTIVE GAS SHIELD APPARATUS/Neil; Stoddard, Yuh	2001-7014850 05/19/00		South Korea
FA 67388 SG	AJT MSS	Stoddard, Yuh	PROTECTIVE GAS SHIELD APPARATUS/Neil; Stoddard, Yuh	200107153-9 05/19/00		Singapore
FA 67388 TW	AJT MSS	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	89109705 05/19/00			Taiwan
EP 67388 EP	AJT MSS	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	00336074-4 05/19/00			Europe
EP 67388 PC	AJT	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, PCT/US00/13754	Closed			PCT

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109912

Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
	MSS	Yuh					
P 67388 -1	AJT MSS	REPLACEABLE VENT SHIELD, SHIM			05/19/00 Unfiled	05/19/00	
P 67735	AJT MSS	IMPROVED TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis, Rao; Kaplin			60/127,520 04/02/99	Closed	
A 67735	AJT MSS	IMPROVED TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis, Rao; Kaplin			09/541,393 03/31/00	6,387,764 Issued: 05/14/02	
PA 67735 CA	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis, Rao; Kaplin			2364975 03/31/00	Abandoned	Canada
PA 67735 CN	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis, Rao; Kaplin			00807742.8 03/31/00		China
PA 67735 IL	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis, Rao; Kaplin Rao			145608 03/31/00	Abandoned	Israel
PA 67735 JP	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis, Rao; Kaplin			2000-610059 03/31/00		Japan
PA 67735 KR	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis, Rao; Kaplin			2001-7012364 03/31/00		South Korea
PA 67735 SG	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis, Rao; Kaplin			200105864-3 03/31/00		Singapore

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1089128

Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	67735	TW	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/ Curtis; Ray; Kaplin	09106191 04/01/00	Taiwan
FB	67735	EP	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/ Curtis; Ray; Kaplin	00919969 03/31/00	
FP	67735	PC	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/ Curtis; Ray; Kaplin	PCT/US04/08650 03/31/00	PTC
P	67736		AJT MSS VEJ	NEAR-ATMOSPHERIC CVD SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS/ Carvalheira; Mayer; Menagh; Savage; Vaughan	60127-532 04/02/99	Closed
A	67736		AJT MSS VEJ	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cassettini; Vaughan; Mayer	094483-943 01/13/00	6,610,150 08/26/03
FA	67736	CA	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cassettini; Vaughan; Mayer	2369042 03/21/00	Abandoned
FA	67736	CN	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cassettini; Vaughan; Mayer	008006632-3 03/21/00	China
FA	67736	IL	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cassettini; Vaughan; Mayer	145678 03/21/00	Abandoned
						Israel

I-7095MASS (463035-826)
1059128

Reference No.		Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
PA	67736 JP	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cozzani; Vaughan; Mayer	2000-602944 03/21/00	Japan
PA	67736 KR	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cozzani; Vaughan; Mayer	2001-701242 03/21/00	South Korea
EA	67736 SG	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cozzani; Vaughan; Mayer	2001059514 03/21/00	Singapore
PA	67736 TW	AJT MSS VEJ	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cozzani; Vaughan; Mayer	89106019 03/31/00	Taiwan
FB	67736 EP	AJT MSS JW	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cozzani; Vaughan; Mayer	0991829.7 03/21/00	Europe
FP	67736 PC	AJT MSS VEJ	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cozzani; Vaughan; Mayer	PCT/US00/07509 03/21/00	PCT
A	67736 1	AJT MSS	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cozzani; Vaughan; Mayer	09767,659 01/22/01	
A	67736 2	AJT	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS	Divisional of 09483,945 filed 01/13/00	

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1089128

Reference No.			Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	67737	AJT MSS VEN	CHAMBERS AND SINGLE-B-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Manig; Carvalho; Trini; Cormier; Vaughan; Meyer	1,127,01 04/02/99		
P	68017	AJT MSS WEN	SINGLE-B-AXIS DUAL-WAFER TRANSFER SYSTEM/Troiani; Cassentine	60,127,650 04/23/99	Merged into P-67736 & Closed	
A	68017	AJT MSS WEN	IMPROVED SURFACE COMPOSITION AND METHOD FOR METAL COMPONENTS/Bailey; Michael; Kane	60,130,783 04/23/99	Closed	
PA	68017	CA MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kane	09,480,730 01/06/00	6,206,973 03/27/01	
PA	68017	CN MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kane	23,735 03/03/00	Abandoned	Canada
PA	67017	IL MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kane	00,808,554,4 03/03/00		China
EA	68017	JP MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kane	14,613,5 03/03/00	Abandoned	Israel
FA	68017	KR MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kane	20,00,613,851 03/03/00		Japan
PA	68017	SG MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kane	2001-7013598 03/03/00		South Korea
FA	68017	TW AJT MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kane	20010613-S 03/03/00		Singapore
FB	68017	HP AJT MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kane	89104518 03/11/00		Taiwan
EP	68017	PC AJT MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kane	00912173,2 03/03/00		Europe
A	68017	1 AJT MSS	CHEMICAL VAPOR DEPOSITION SYSTEM AND METHOD/Bailey; Michael; Kane	PCT/US00/05630 03/03/00	Closed	PCT
				09,704,644 11/01/00	6,485,783	

I-71925A5S (463035-828)
1039126

Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P 68048		WEN	AJT	EQUAL FLOW SPLIT GAS DELIVERY APPARATUS/Bartolomew; Yuh; Stumbo; King; Chan	60/134,443 05/17/99	11/26/02 Closed	
A 68048		MSS WEN	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	09/494,620 01/31/00	Abandoned	
FA 68048	CA	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	2308832 05/15/00	Abandoned	Canada	
FA 68048	CN	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	00108549-2 05/17/00		China	
FB 68048	EP	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	00304070-6 05/15/00		Europe	
PA 68048	HK	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	01102640-9 04/12/01	Abandoned	Hong Kong	
FA 68048	JP	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	2000-144513 05/17/00		Japan	
FA 68048	KR	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	2000-0026827 05/16/00		South Korea	
FA 68048	MY	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	PI200002031 05/10/00		Malaysia	
FA 68048	SG	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	200002470-3 05/09/00	87112 10/16/02	Singapore	
FA 68048	TH	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh; Stumbo; King; Chan	057634 05/16/00	Abandoned	Thailand	
FA 68048	TW	AJT	GAS DISTRIBUTION SYSTEM/Bartolomew; Yuh;	89109368			Taiwan

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 68048 1	MSS WEN	Stumberg; King; Chen	Mark; King; Chen	05/16/00		
P 68073	AJT MSS	GAS DISTRIBUTION SYSTEM/Bertholdmeyer; Yuh; Marc; King; Chen		10/219,924. 08/14/02	Abandoned	
A 68073	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE BY USING ALKYSILOXANE OLIGOMERS WITH OZONE FOR SUB 0.18 MICRON DEVICE APPLICATIONS IN VLSI/Jain; Yuan		60/143,198 07/09/99	Closed	
FA 68073 CN	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE BY USING ALKYSILOXANE OLIGOMERS WITH OZONE FOR SUB 0.18 MICRON DEVICE APPLICATIONS IN VLSI/Jain; Yuan		09/542,612 04/04/00	6465044 10/15/02	China
FA 68073 JP	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYSILOXANE OLIGOMERS WITH OZONE/Jain; Yuan		00811030.1 06/15/00		Japan
FA 68073 KR	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYSILOXANE OLIGOMERS WITH OZONE/Jain; Yuan		2001-509075 06/15/00		South Korea
FA 68073 SG	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYSILOXANE OLIGOMERS WITH OZONE/Jain; Yuan		2002-7000308 06/15/00		Singapore
FA 68073 TW	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYSILOXANE OLIGOMERS WITH OZONE/Jain; Yuan		89113435 07/06/00	153183 07/25/02	Taiwan
EP 68073	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYSILOXANE OLIGOMERS WITH OZONE/Jain; Yuan		09/39940.3 06/15/00		Europe
EP 68073 PC	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYSILOXANE OLIGOMERS WITH OZONE		PCT/US00/16642 06/15/00	Closed	PCT
P 68044	AJT	METHOD FOR IN SITU CLEANING OF SILICON		60143,285	Closed	

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1099128

Reference No.	Title/Inventor			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 68244	MSS	AJT	DIOXIDE DEPOSITION CHAMBERS USING COMBINATION FLUORINE CHEMISTRIES/Mayer, et al.	09/615,035 07/12/00	6,544,345 04/08/03	
FA 68244	CN	AJT MSS	METHOD FOR IN-SITU CLEANING OF SILICON DIOXIDE DEPOSITION CHAMBERS USING COMBINATION FLUORINE CHEMISTRIES/Mayer, et al.	09/615,035 07/12/00	00811232.0 07/12/00	China
FA 68244	JP	AJT MSS	METHOD AND SYSTEM FOR IN-SITU CLEANING OF SEMICONDUCTOR MANUFACTURING EQUIPMENT USING COMBINATION CHEMISTRIES/Mayer, et al.	2001-509320 07/12/00	2001-509320 07/12/00	Japan
FA 68244	KR	AJT MSS	METHOD AND SYSTEM FOR IN-SITU CLEANING OF SEMICONDUCTOR MANUFACTURING EQUIPMENT USING COMBINATION CHEMISTRIES/Mayer, et al.	2002-70003480 07/12/00	2002-70003480 07/12/00	South Korea
FA 68244	SG	AJT MSS	METHOD AND SYSTEM FOR IN-SITU CLEANING OF SEMICONDUCTOR MANUFACTURING EQUIPMENT USING COMBINATION CHEMISTRIES/Mayer, et al.	2002-00181-6 07/12/00	2002-00181-6 07/12/00	Singapore
FA 68244	TW	AJT MSS	METHOD FOR IN-SITU CLEANING OF SILICON DIOXIDE DEPOSITION CHAMBERS USING COMBINATION FLUORINE CHEMISTRIES/Mayer, et al.	89113887 07/18/00	89113887 07/18/00	Taiwan
EP		AJT MSS TH	METHOD AND SYSTEM FOR IN-SITU CLEANING OF SEMICONDUCTOR MANUFACTURING EQUIPMENT USING COMBINATION CHEMISTRIES/Mayer, et al.	00958006.9 07/12/00	00958006.9 07/12/00	Europe
EP		AJT MSS	METHOD FOR IN-SITU CLEANING OF SILICON DIOXIDE DEPOSITION CHAMBERS USING COMBINATION FLUORINE CHEMISTRIES/Mayer, et al.	PCT/US00/40359 07/12/00	PCT/US00/40359 07/12/00	PCT
P	68628	AJT	SYSTEM AND METHOD FOR DEPOSITING	60/166,662	Closed	Closed

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1059726

Reference No.	Title/Inventor			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 68628	MSS	AJT	INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Feltz	11/19/99		
A 68628	MSS	AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Feltz	09/715,455 11/17/00		
FA 68628 CN	MSS	AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Feltz	00816928.4 11/17/00		China
FA 68628 JP	MSS	AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Feltz	2001-538578 11/17/00		Japan
FA 68628 KR	MSS	AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Feltz	11/17/00		South Korea
FA 68628 MY	MSS	AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Feltz	P12005431 11/20/00		Malaysia
FA 68628 SG	MSS	AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Feltz	11/17/00		Singapore
FA 68628 TW	MSS	AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS	89124488 11/18/00		Taiwan
EP 68628	EP	AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Feltz	00980511.0 11/17/00		Europe
EP 68628 PC	MSS	AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Feltz	PC1US0031694 11/17/00	Closed	PCT
A 68894	MSS	AJT	CHEMICAL VAPOR DEPOSITION APPARATUS/Campbell; Miller	06412,237 08/22/82	4,545,327 10/08/85	
FA 68894 AU	MSS	AJT	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	18480/83 08/26/83	538152 08/26/83 Abandoned	Australia
FA 68894 CA	MSS	AJT	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	435,134 08/23/83	1,196,777. 11/19/85	Canada

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Reference No.			Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
PA	68894	IL	AJT MSS	CHEMICAL VAPOR DEPOSITION PROCESS/ Campbell; Miller	69170 07/06/83	Abandoned
PA	68894	IL-1	AJT MSS	CHEMICAL VAPOR DEPOSITION PROCESS/ Campbell; Miller	80079 07/06/83	07/01/87 Abandoned
PA	68894	JP	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	155171/83 08/26/83	1446905 06/30/88
FE	68894	EP	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	83304989.5	Abandoned
A	68894	I	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	06/637313 10/02/84	4,547,404 10/15/85
A	68895	AU	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	065528193 08/31/83	4,539,933 09/10/85
PA	68895	CA	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	32564/84 08/30/84	572883 08/30/84
PA	68895	CA-1	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	462,110 08/30/84	1,216,419 01/13/87
PA	68895	TW	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	515,262 08/01/86	1,236,970 05/24/88
PA	68895	EP	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	73103396 08/30/84	23307 12/28/85
FE	68896	R	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Foster; Herring	84305932.0 08/30/84	0157702 03/21/90
A	68896	R	AJT MSS	CHEMICAL VAPOR DEPOSITION WAVER BOAT/ Foster; Herring	061628,542 07/06/84	4,548,159 10/22/85
PA	68896	R	AJT MSS	CHEMICAL VAPOR DEPOSITION WAVER BOAT/ Foster; Herring	146357/85 07/05/85	1451172 07/25/88
						Abandoned

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1099128

Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 68897	AT	Chemical Vapor Deposition Wafer Boat/ Lean; DuBois	06/607,065	4,582,020			
FA 68897 CA	AT	Chemical Vapor Deposition Wafer Boat/ Lean; DuBois	03/04/84	04/15/86			
FA 68897 JP	AT	Chemical Vapor Deposition Wafer Boat/ Lean; DuBois	04/25/85	1,234,972	04/12/88	Abandoned	Canada
A 68897 1	AT	Chemical Vapor Deposition Wafer Boat/ Lean; DuBois	05/02/85	1,604,459	04/22/91	Japan	
A 68897 2	AT	Chemical Vapor Deposition Wafer Boat/ Lean; DuBois	06/804,954	4,641,604	02/10/87	Abandoned	
A			12/03/85 Continuation of 06/607,065				
A			06/607,065				
FA 68898 CA	AT	Primary Flow CVD Apparatus Comprising Gas Preheater and Means for Substantially Eddy-Free Gas Flow/Lean;	07/691,470	5,320,680	05/14/94		
FA 68898 JP	AT	Primary Flow CVD Apparatus and Method/ Lean; DuBois; Miller; Schleimer	04/25/91			Abandoned	
FA 68898 KR	AT	Primary Flow CVD Apparatus and Method/ Lean; DuBois; Miller; Schleimer	2,109,198	21,091,98	03/28/00	Abandoned	Canada
FA 68898 CH	AT	Primary Flow CVD Apparatus and Method/ Lean; DuBois; Miller; Schleimer	04/09/92				
FA 68898 DE	AT	Primary Flow CVD Apparatus and Method/ Lean; DuBois; Miller; Schleimer	5,108,624/2	3,193,716			
FA 68898 EP	AT	Primary Flow CVD Apparatus and Method/ Lean; DuBois; Miller; Schleimer	04/09/92	05/25/01			
FA 68898 FR	AT	Primary Flow CVD Apparatus and Method/ Lean; DuBois; Miller; Schleimer	7,032,34/1993	02,67,520	07/05/00	South Korea	
FA 68898 DE	AT	Primary Flow CVD Apparatus and Method/ Lean; DuBois; Miller; Schleimer	04/09/92	05,853,43	12/08/99	Abandoned	Switzerland
FA 68898 EP	AT	Primary Flow CVD Apparatus and Method/ Lean; DuBois; Miller; Schleimer	9,291,185,52	6,923,04/01,0	12/08/99	Germany	
FA 68898 FR	AT	Primary Flow CVD Apparatus and Method/ Lean; DuBois; Miller; Schleimer	04/09/92	05,853,43	12/08/99	Europe	
			9,291,185,52	05,853,43			France

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Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
EP 68898 GB	MSS AJT MSS	Lean; DuBois; Miller; Schleimer Lean; DuBois; Miller; Schleimer Lean; DuBois; Miller; Schleimer	PRIMARY FLOW CVD APPARATUS AND METHOD/ PRIMARY FLOW CVD APPARATUS AND METHOD/ PRIMARY FLOW CVD APPARATUS AND METHOD/	04/09/92 04/09/92 04/09/92	0685343 0685343 0685343	United Kingdom
EP 68898 IT	AJT MSS	Lean; DuBois; Miller; Schleimer	PRIMARY FLOW CVD APPARATUS AND METHOD/	04/09/92	12/08/99	Italy
EP 68898 NL	AJT MSS	Lean; DuBois; Miller; Schleimer	PRIMARY FLOW CVD APPARATUS AND METHOD/	04/09/92	12/08/99	
EP 68898 PC	AJT MSS	Lean; DuBois; Miller; Schleimer	PRIMARY FLOW CVD APPARATUS AND METHOD/	04/09/92	12/08/99	Netherlands
A 68899	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalek	08/399,108 08/399,108	04/09/92 03/03/95	5,626,680 05,069/97	PCT
A 68899 1	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalek	08/565,177 11/28/95	11/28/95	5,679,168 10/21/97	
EP 68899 1-PC	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalek	CIP of 08/399,108	PCTUS96/02440	Closed	PCT
EP 68899 1-EP	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalek	03/04/96	03/04/96		Europe
EP 68899 1-JP	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalek	96906598.6 03/04/96:	96906598.6 03/04/96:		Japan
EP 68899 1-KR	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalek	526893/96 09/01/97	526893/96 09/01/97		South Korea
A 68899 2	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Ratliff	706100/1997 11/28/95	09/02/97 CIP of 08/399,108	08/563,875 04/08/97	
EP 68899 2-PC	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Ratliff	5,618,351 04/08/97	PCTUS96/18731 11/22/96	Closed	PCT
EP 68899 2-EP	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Ratliff	0864170	0864170		Europe
EP 68899 2-JP	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Ratliff	520565/97 11/22/96	520565/97 11/22/96		Japan
EP 68899 2-KR	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Ratliff	70360/1998 11/22/96	70360/1998 11/22/96		South Korea

Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
PA 68899 2-TW	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Kob, K.; Dip; Engdahl; Oliver; Ratiff		MSS	86101168 01/31/97	NI-094773 06/11/98	Taiwan
A 68900	AJT	METHOD OF LOADING AND UNLOADING A FURNACE/Altidge; Holloway; Fritz; Gott; Herrera		MSS	06719409 04/03/85	4,636,140 01/13/87	
A 68900 1	AJT	SEMICONDUCTOR WAFER BOAT LOADER RELEASEABLE MOUNTING/Altidge; Holloway; Fritz; Gott; Herrera		MSS	06889460 06/30/86	4,721,424 01/26/88	
A 68900 2	AJT	SEMICONDUCTOR WAFER FURNACE DOOR/ Altidge; Holloway; Fritz; Gott; Herrera		MSS	06880422 06/30/86	4,692,115 09/08/87	
A 68900 3	AJT	SEMICONDUCTOR WAFER BOAT LOADER CONTROL SYSTEM		MSS	06880423 06/30/86	4,684,863 08/04/87	
A 68901	AJT	GAS SCAVENGER/Taylor		MSS	06919736 10/16/86	4,711,197 12/08/87	
PA 68901 CA	AJT	GAS SCAVENGER/Taylor		MSS	546,025 08/21/87	1,277,442 12/04/90	Canada
PA 68901 JP	AJT	GAS SCAVENGER/Taylor		MSS			Abandoned
A 68902	AJT	THERMAL PROCESSING APPARATUS/Kowalek; Ratiff; Koble; Park; Yang		MSS	26150787 10/16/87	2642936 05/02/97	Japan
PA 68902 KR	AJT	THERMAL PROCESSING APPARATUS/Kowalek; Ratiff; Koble; Park; Yang		MSS	088271542 03/22/97	6,005,225 12/21/99	
PA 68902 JP	AJT	THERMAL PROCESSING APPARATUS/Kowalek; Ratiff; Koble; Park; Yang		MSS	107871998 03/27/98		South Korea
PA 68902 TW	AJT	THERMAL PROCESSING APPARATUS/Kowalek; Ratiff; Koble; Park; Yang		MSS	9518698 03/25/98		Japan
PE 68902 EP	AJT	THERMAL PROCESSING APPARATUS/Kowalek; Ratiff; Koble; Park; Yang		MSS	87104418 03/24/98		Taiwan
A 68902 1	AJT	SEMICONDUCTOR THERMAL PROCESSOR WITH		MSS	983401618.9 03/03/98		Europe
		I-71935/MSS (463035-828)			09/022,057	6,059,567	

Reference No.	The Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 68902 1-AU	MSS	AJT	RECIRCULATING HEATER EXHAUST COOLING SYSTEM/Bolton; Wiesen	02/10/98 CTP of 09/22/7,542	05/09/00	
FA 68902 1-CA	MSS	AJT	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	1551199 02/08/99		Australia
FA 68902 1-CA	MSS	AJT	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	2,261,391		Canada
FE 68902 1-EP	MSS	AJT	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	02/08/99		Europe
FE 68902 1-HK	MSS	AJT	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	99300910.9 02/09/99		
FA 68902 1-IP	MSS	AJT	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	00100999.1 02/18/00		Hong Kong
FA 68902 1-KR	MSS	AJT	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	11-072438 02/10/99		Japan
FA 68902 1-KR	MSS	AJT	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	4922/1999 02/09/99		South Korea
A 68903 CA	AJT	DOUBLE WALL REACTION CHAMBER MSS/WIEN GLASSWARE/Fowler; Parvin; Kowaldt; Wiesen	09/022,056 02/10/98	6,101,844 08/15/00		
FA 68903 AU	AJT	DOUBLE WALL REACTION CHAMBER MSS/WIEN GLASSWARE/Fowler; Parvin; Kowaldt; Wiesen	15512/99 02/08/99	746022 07/25/02		Australia
FA 68903 JP	AJT	DOUBLE WALL REACTION CHAMBER MSS/WIEN GLASSWARE/Fowler; Parvin; Kowaldt; Wiesen	2,261,394 02/08/99	Abandoned		Canada
FA 68903 KR	AJT	DOUBLE WALL REACTION CHAMBER MSS/WIEN GLASSWARE/Fowler; Parvin; Kowaldt; Wiesen	11-072437 02/10/99			Japan
FE 68903 HK	AJT	DOUBLE WALL REACTION CHAMBER MSS/WIEN GLASSWARE/Fowler; Parvin; Kowaldt; Wiesen	4911/1999 02/09/99			South Korea
FE 68903 HK	AJT	DOUBLE WALL REACTION CHAMBER MSS/WIEN GLASSWARE/Fowler; Parvin; Kowaldt; Wiesen	99300909.1 02/09/99			Europe
P 68905	AJT	LINEAR RTP REACTOR/Kowaldt; Ratiff; Sub; Qin MSS	00100998.2 02/18/00		Abandoned	Hong Kong
A 68905	AJT	HOT WALL RAPID THERMAL PROCESSOR/Ratiff; Qir; Kowaldt; Yedoloff; Seethi MSS	60/096,283 08/12/98	Closed		
P 68905 1	AJT	HOT WALL RAPID THERMAL PROCESSOR/Ratiff	09/373,894 08/12/99	6,300,600 10/09/01		
			60/217,321	Closed		

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 68905 1	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald	07/07/00	6,462,310 08/11/00	
FP 68905 1-PC	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald	PCT/US00/22202 08/11/00	Closed	PCT
EA 68905 1-CN	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald; Qin	08/11/00	00812823,5 08/11/00	China
FA 68905 1-JP	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald; Qin	2001-517110 08/11/00		Japan
FA 68905 1-KR	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald; Qin	2002-7001786 08/11/00		South Korea
FA 68905 1-MY	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald; Qin	P1 20003683 08/11/00		Malaysia
FA 68905 1-SG	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald; Qin	Unfiled		Singapore
FA 68905 1-TW	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald	89116281 08/11/00	149415 05/17/02	Taiwan
FB 68905 1-EP	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald; Qin	00937426,0 08/11/00		Europe
A 68905 2	MSS	AJT	HOT WALL RAPID THERMAL PROCESSOR/Kowald	09/934,932 08/21/01	6,492,621 12/10/02	
A 68905 3	MSS		HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald	10/262,215 09/30/02		
A 68905 4	MSS		HOT WALL RAPID THERMAL PROCESSOR/Radiif, Kowald	10/261,963 09/30/02		
A 68905 5	MSS		HOT WALL RAPID THERMAL PROCESSOR			
A 68906	MSS	AJT	SUBSTRATE LOADING MEANS FOR A CHEMICAL VAPOR DEPOSITION APPARATUS/Campbell; Dubai; Minister; Miller	06/529,415 09/06/03	4,524,719 06/25/85	
A 68907		AJT	LOW TEMPERATURE SILICON NITRIDE CVD	06/839,923	4,720,395	

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Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
		MSS	PROCESS			
A 68908	AJT	PULSE WIDTH MODULATED PRESSURE CONTROL SYSTEM FOR CHEMICAL VAPOR DEPOSITION APPARATUS	Jr., Johnson; Elliott	06/245,212 03/27/86 CIP of 06/813,915	4,728,269 03/01/88	Abandoned
A 68909	AJT	HOT WALL DIFFUSION FURNACE AND METHOD FOR OPERATING THE FURNACE	Jr., Faic; Enamul	07/181,787 04/15/88	4,886,954 12/12/89	
A 68910	AJT	METHOD AND APPARATUS FOR REMOVAL OF BY-PRODUCTS OF CHEMICAL VAPOR DEPOSITION FROM OIL FOR VACUUM PUMP/FILTER		06/029,525 04/12/79	4,228,004 10/14/80	
A 68911	AJT	MASS FLOW CONTROLLER	Doyle	06/193,876 10/03/80	4,658,855 04/21/87	
A 68912	AJT	DIFFUSION FURNACE MULTIZONE TEMPERATURE CONTROL	Yn	06/784,676 05/19/86	4,711,989 12/08/87	
A 68913	AJT	WAFER BOAT TRANSFER TOOL	Mello	06/783,963 05/16/86	4,728,246 03/01/88	Abandoned
A 68914	AJT	WAFER TRANSFER STAND	Sander; Taylor	07/048,863 05/12/87	4,721,427 01/26/88	Abandoned Reinstated
A 68915	AJT	TEMPERATURE SENSOR FOR BATCH-TYPE REACTOR/REFINING		09/024,500 02/17/98	Abandoned	
A 68916	AJT	LAYERED BLOCK FLUID DELIVERY SYSTEM	Nguyen; Vej	09/388,216 09/01/99	Abandoned	
PA 68916	TW	LAYERED BLOCK FLUID DELIVERY SYSTEM		89116370 08/14/00	14,6378 08/21/01	Taiwan
PP 68916	PC	LAYERED BLOCK FLUID DELIVERY SYSTEM		US09/21227 08/03/00	Abandoned	PCT

Reference No.	Title/Inventors			Serial No/ Filing Date	Patent No/ Issue Date	Foreign Countries
A 68916 1	AJT MSS Vej	MODULAR FLUID DELIVERY SYSTEM/Nguyen		09/200,595 03/06/01 CIP of 09/388,216 09/01/99		
PA 68916 1-CN	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen		02106830,5 03/05/02		China
PA 68916 1-P	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen		2002-059114 03/05/02		Japan
PA 68916 1-KR	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen		2002-0011854 03/06/02		South Korea
PA 68916 1-MY	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen		P120020747 03/01/02		Malaysia
PA 68916 1-SG	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen		20020201-1 02/27/02		Singapore
PA 68916 1-TW	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen		911003478 02/26/02		Taiwan
EE 68916 1-EP	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen		02251573,8 03/06/02		Europe
P 69013	MSS	FLUOROPOLYMER INTERLAYER DEPOSITION/Bye; Loper; Macell;		05/04/01 (Filed by Dn Post)		Co-owned with Dupont
A 69013	AJT MSS	DEPOSITION OF FLUOROPOLYMER FILMS/Macella; Roes; Loper; Peat; Tally; Young		Unfiled		
A 69173	MSS	MODEL BASED TEMPERATURE CONTROL OF BATCH FURNACE/OH		Unfiled		
A 69174	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Naq; Saq; Oh		09/628,471 07/31/00	6,476,921 11/05/02	Co-owned with MIT, all foreign as well
P 69174 1	MSS	IN-SITU SENSING AND ENDPOINT DETECTION IN COPPER CMP/Saq; Li; Oh		60258,931 12/29/00	Closed	
A 69174 1	AJT MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Saq; Li; Oh		10,029,080 12/21/01		Co-owned with MIT, all foreign as well

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Reference No.	The Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 69174 I-CN MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION			N/A 07/31/01		China
FA 69174 I-JP MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION			2002-516696 01/31/01		Japan
FA 69174 I-KR MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION			2003-7001394 01/31/01		S. Korea
FA 69174 I-MY AJT MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Nam; Saler; Oh			FI20013602 07/31/01		Malaysia
FA 69174 I-SG MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION			2003006624 01/31/01		Singapore
FA 69174 I-TW MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Nam; Saler; Oh			90118624 07/31/01	158247. 10/18/02	Taiwan
IP 69174 I-PC MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Nam; Sub; Oh			PCT/TW01/24146 07/31/01	Closed	PCT
A 69175 MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OR SUBSTRATES/Malvin; Sr; Oh			09/628,563 07/31/00		Co-owned with MIT, all foreign as well
FA 69175 MY MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Malvin; Sr; Oh			PI20013601 07/31/01		Malaysia
FA 69175 TW MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Malvin; Sr; Oh			90118623 07/31/01		Taiwan
P 69175 I MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Malvin; Sub; Oh			60/229,016 12/29/00	Closed	
	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Sub; Malvin; Oh			10/110,000 02/27/01		Co-owned with MIT, all foreign as well
FA 69175 I-CN MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING			01815145.0 01/31/01		China

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1089122

Reference No.		Title/Inventor	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	69175 1-JP	MSS APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	2002-515445 01/31/01		Japan
FA	69175 1-KR	MSS APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	2003-7001395 01/31/01		South Korea
FA	69175 1-SG	MSS APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	200300678-0 01/31/01		Singapore
FA	69175 1-EP	MSS APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	190223362- 01/31/01		Europe
EP	69175 1-PC	MSS APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	PCT/US01/41513 07/31/01		PCT
A	69175 2	MSS APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	Closed		
A	69228	MSS METHOD OF CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	09/628,962 07/31/00	6438,013 10/01/02	Co-owned with MIT, all foreign as well
FA	69228 CN	MSS METHOD OF CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	01815147.7 07/31/01		China
FA	69228 JP	MSS METHOD OF CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	2002-515446 07/31/01		Japan
FA	69228 KR	MSS METHOD OF CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	2003-7001400 07/31/01		South Korea
FA	69228 MY	MSS METHOD OF CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	PCT/US01/24170 07/31/01		Malaysia
EP	69228 PC	MSS METHOD OF CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	PCT/US01/24170 07/31/01		PCT
FA	69228 SG	MSS METHOD OF CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	200300663-2 07/31/01		Singapore
FA	69228 TW	MSS METHOD OF CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	90113625 07/31/01		Taiwan
EP	69228 EP	MSS METHOD OF CHEMICAL MECHANICAL POLISHING/Lit; Saks; Oh	019573815 07/31/01		Europe
P	69229	MSS MECHANISMS OF MATERIAL REMOVAL IN THE CHEMICAL MECHANICAL POLISHING PROCESS/ I-71935/MSS (463035-226) 1059128	60/263,813 01/23/01	Closed	

Reference No.		Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries			
A	69229	MSS	Lai; Salas; Chen					
		CHEMICAL MECHANICAL POLISHING OF COPPER-OXIDE DAMASCENE STRUCTURES/Sakai; Lai; Oh	10057477 01/23/02		Co-owned with MIT; all foreign as will			
FP	69229	PC	MSS	CHEMICAL MECHANICAL POLISHING OF COPPER-OXIDE DAMASCENE STRUCTURES/Sakai; Lai; Oh	01/23/02	PCT		
A	69274	MSS	Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	METHOD AND APPARATUS FOR TRANSFERRING WAFERS BETWEEN CASSETTES AND A BOAT/ Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	06864,077 05/16/86	4,770,590 09/13/88		
EP	69274	MSS	Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	METHOD AND APPARATUS FOR TRANSFERRING WAFERS BETWEEN CASSETTES AND A BOAT/ Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	05/21/01	90006,018	Re-examination of Patent No. 4,770,590	
FA	69274	DE	MSS	METHOD AND APPARATUS FOR TRANSFERRING WAFERS BETWEEN CASSETTES AND A BOAT/ Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	05/09/87	P3715601.2 01/24/96	315787. 07/06/00	Germany
FA	69274	DE-1	MSS	METHOD AND APPARATUS FOR TRANSFERRING WAFERS BETWEEN CASSETTES AND A BOAT/ Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	05/09/87	P3745134.0	03/04/99	Germany
FA	69274	FR	MSS	WAFFER TRANSFERRING APPARATUS/Hartinger; Nishikawa; Schuman; Yee	8706851 05/15/87	8706851 08/21/92	France	
FA	69274	FR-1	MSS	WAFFER TRANSFERRING APPARATUS/Hartinger; Nishikawa; Schuman; Yee	8716024 11/19/87	8716024 08/21/92	France	
FA	69274	IT	MSS	METHOD AND APPARATUS FOR TRANSFERRING WAFERS BETWEEN CASSETTES AND A BOAT/ Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	47930A/87 05/14/87	1206233 04/14/89	Italy	
FA	69274	P	MSS	METHOD AND APPARATUS FOR TRANSFERRING WAFERS BETWEEN CASSETTES AND A BOAT/ Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	62-117197 05/15/87	2631055 08/08/97	Japan	
FA	69274	GB	MSS	METHOD AND APPARATUS FOR TRANSFERRING WAFERS BETWEEN CASSETTES AND A BOAT/ Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	8711230 05/13/87	2190345 08/15/90	Great Britain	
FA	69274	GB-1	MSS	METHOD AND APPARATUS FOR TRANSFERRING WAFERS BETWEEN CASSETTES AND A BOAT/ Hughes; Webber; Hartinger; Nishikawa; Schuman; Yee	8922730.0 05/13/87	2223470 08/14/90	Great Britain	

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 69447	MSS	NON-CONTACT CMP MACHINE		60/274,532 03/08/01	CLOSED PER CLIENT	
P 69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA-T/Porter, Shamer		10095,974 03/08/02		
A 69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter, Shamer		PCT/US02/07034 03/08/02	PCT	
PP 69447	PC	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter, Shamer				
FA 69447	CN	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter, Shamer		0280895,3 03/08/02		China
FA 69447	JP	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter, Shamer		2002/572612 03/08/02		
FA 69447	KR	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter, Shamer		2002-7014904 03/08/02		Japan
FA 69447	MY	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter, Shamer		P20022469 06/28/02		South Korea
FA 69447	SG	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter, Shamer		200206993-0 03/08/02		Malaysia
FA 69447	TW	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter, Shamer		91114419 06/25/02		Singapore
FB 69447	EP	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter, Shamer		027079649 03/08/02		Taiwan
P 69448	MSS	INERTIAL TEMPERATURE CONTROL/Shamer		60/266,926 02/06/01	Closed	Europe
A 69448	MSS	INERTIAL TEMPERATURE CONTROL/Shamer		10/058,127 02/06/02		
FA 69448	CN	MSS	INERTIAL TEMPERATURE CONTROL/Shamer	021080832 02/06/02		China
FA 69448	JP	MSS	INERTIAL TEMPERATURE CONTROL/Shamer	2002-069336 02/06/02		Japan
FA 69448	KR	MSS	INERTIAL TEMPERATURE CONTROL/Shamer	2002-6778 02/06/02		South Korea
FA 69448	MY	MSS	INERTIAL TEMPERATURE CONTROL/Shamer	P20020366 02/04/02		Malaysia

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Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 69448 SG MSS	Inertial Temperature Control	Stamer			200200733-4 02/06/02		Singapore
FA 69448 TW MSS	Inertial Temperature Control	Stamer			91101797 02/01/02	173549 07/07/03	Taiwan
FB 69448 EP MSS	Inertial Temperature Control	Stamer			022508147 02/06/02		Europe
A 69477 MSS	NON-CONTACT CMP MACHINE	Sub				Closed	
P 69829 MSS	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SiOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES	Mayer; Ingle; Murphy; Matson; Katin			60/335,494 11/01/01	Closed	
A 69829 MDV	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SiOX THIN FILMS ON SILICON SURFACE RELATIVE TO SILICON-NITRIDE SURFACES	Mayer; Ingle; Murphy; Matson; Katin			10285,966 11/01/02		
FA 69829 CN MSS	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SiOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES	Mayer; Ingle; Murphy; Matson; Katin			11/01/02		China
FA 69829 JP MSS	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SiOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES	Mayer; Ingle; Murphy; Matson; Katin			2002-320226 11/01/02		Japan
FA 69829 KR MSS	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SiOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES	Mayer; Ingle; Murphy; Matson; Katin					South Korea
FA 69829 MY MSS	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SiOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES	Mayer; Ingle; Murphy; Matson; Katin			PL20024020 10/28/02		Malaysia

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109128

Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
	PA	69829	SG	MSS	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O ₃ BASED SiOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Matson; Kruis	200206557-1 10/29/02	Singapore
PA	69829	TW	MSS	MDV MBG	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O ₃ BASED SiOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Matson; Kruis	91123270 10/25/02	Taiwan
EP	69829	EP	MSS	MDV MBG	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O ₃ BASED SiOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Matson; Kruis	02257608.6 01/01/02	Europe
P	70028		MSS		MULTILAYER HIGH DIELECTRIC CONSTANT OXIDE FILMS AND METHOD OF MAKING/Senzaki	600264428 01/26/01	
A	70028		MSS		MULTILAYER HIGH-k GATE OXIDE THIN FILMS/Senzaki	100056625 01/25/02	
P	70292		ATJ		FLUOROPOLYMER INTERLAYER DIELECTRIC BY CHEMICAL VAPOR DEPOSITION/Mocella; Feiring, Treit, Bischko, Lopata, Rose	600288633 05/04/01	Application is co-owned with DuPont
	No Dasy Ref. number.		MSS		No Dasy Ref. number.	10137875 May 2, 2002	To be filed by DuPont counsel
P	70380		MSS	MDV	HIGH FLOW RATE BUBBLER WITH A LIQUID PHASE EVAPORATOR/Takemoto	60337566 11/30/01	Application is co-owned with DuPont
A	70380		MSS	MDV	HIGH FLOW RATE BUBBLER WITH A LIQUID PHASE EVAPORATOR/Takemoto	11/27/02	To be filed by DuPont counsel
PA	70380	MY	MSS		HIGH FLOW RATE BUBBLER SYSTEM AND METHOD; Takemoto	P1 20024434 11/27/02	Malaysia

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1099128

10/8/2003

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 70380 TW MSS	HIGH FLOW RATE BUBBLER SYSTEM AND METHOD; Tatsumi			91134329 11/26/02		Taiwan
FA 70380 PC MSS	HIGH FLOW RATE BUBBLER SYSTEM AND METHOD; Tatsumi			US02/38178 11/27/03		PCT
P 70381 WEN	APPARATUS AND METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes			60/313,719 08/20/01	Closed	
A 70381 WEN	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes			10/224,687 08/20/02		
FA 70381 CN MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes			02143436.5 08/19/02		China
FA 70381 JP MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes			2002-280056 08/20/02		Japan
FA 70381 KR MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes			2002-0049154 08/20/02		South Korea
FA 70381 MY MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes			08/20/02		
FA 70381 SG MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes			P124023050 08/19/02		Malaysia
FA 70381 TW AJT	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Draper; Robinson; Lopes			20020046-6 08/19/02		Singapore
FA 70381 MBG MSS	APPARATUS & METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Draper; Robinson; Lopes			91118697 08/19/02		Taiwan
FE 70381 EP MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes			02255775.5 08/20/02		Europe
A 70466 MSS	CHEMICAL VAPOR DEPOSITION SYSTEM FOR DEPOSITING FLUOROPOLYMER FILMS/Lopes			Closed		
P 70524 MSS	MODULAR INJECTOR AND EXHAUST ASSEMBLY/ DaDontay; Methicev; Kuria			60/305,406 07/13/01	Closed	
A 70524 MSS	MODULAR INJECTOR AND EXHAUST ASSEMBLY/ DaDontay; Methicev; Kuria			10/194,639 07/12/02		
PA 70524 CN TII MSS	MODULAR INJECTOR/DeDentay; Methicev; Kuria	MBG		02141805.5 07/15/02		China

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Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 70524 JP MSS TH MBG	MODULAR INJECTOR/DeDentley; Mathiesen; Kurita	Kurita	2002-0040964	07/13/02			Japan
FA 70524 KR MSS TH MBG	MODULAR INJECTOR/DeDentley; Mathiesen; Kurita	Kurita	P20022636	07/11/02			South Korea
FA 70524 MY MSS TH MBG	MODULAR INJECTOR/DeDentley; Mathiesen; Kurita	Kurita	2002042261	07/12/02			Malaysia
FA 70524 SG MSS TH MBG	MODULAR INJECTOR/DeDentley; Mathiesen; Kurita	Kurita	2002042268	07/12/02			Singapore
FA 70524 TW MSS TH MBG	MODULAR INJECTOR/DeDentley; Mathiesen; Kurita	Kurita	91113568	07/12/02			Taiwan
FB 70524 EP MSS TH MBG	MODULAR INJECTOR/DeDentley; Mathiesen; Kurita	Kurita	02254963.8	07/15/02			Europe
A 70824	HEATING SYSTEM AND METHOD FOR HEATING AN ATMOSPHERIC REACTION/Breden; Seidemann; Koester	Seidemann; Koester	Prepared and Prosecuted by Infineon counsel		This patent application is co-owned with Infineon	[related opened matter: Pat. Appl. # MY-02120021354; TW-091107447; PC-PCT/EP0204069]	
P 70859	DEPOSITION OF LOW STRESS GERMANIUM AND BORON DOPED SILICA FILMS FOR OPTICAL WAVEGUIDE/Mogard	Mogard	60710,026- Closed	08/03/01			
A 70859	OXIDE STRUCTURE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	Mogard	10/210,978	08/02/02			
FA 70859 CN MSS	OXIDE STRUCTURE USABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	Mogard	08/08/02				China
FA 70859 JP MSS	OXIDE STRUCTURE USABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	Mogard	2002-262112	08/05/02			Japan
FA 70859 KR MSS	OXIDE STRUCTURE USABLE FOR OPTICAL		2002-0045980				South Korea

I-70859/MASS (46385-828)
1059128

Reference No.		Title/Inventor		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	70859	MY	MSS	WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	08/03/02	
FA	70859	SG	MSS	OXIDE STRUCTURE USABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	PI200225907 08/02/02	Malaysia
FA	70859	TW	MSS	OXIDE STRUCTURE USABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	200204671-2 08/02/02	Singapore
FE	70859	EP	MSS MDV MBG	OXIDE STRUCTURE USABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	9111477 08/02/02	Taiwan
A	70888		MSS TH	DEPOSITION OF LOW STRESS GERMANIUM AND BORON DOPED SILICA FILMS FOR OPTICAL WAVEGUIDES/Mogard	022534299 08/02/02	Europe
P	70893		MSS	BELLOWS ROTARY FEED-THROUGH SEAL/H2	Closed	
A	70893		MSS	AN IMPROVED DESIGN FOR A LINEAR INJECTOR ASSEMBLY/Matheson; Halimelby; Bartholomew; Pat; Yuh	60314,762 08/24/01	Closed
FA	70893	MY	MSS MBG	PROTECTIVE SHIELD AND SYSTEM FOR GAS DISTRIBUTION SYSTEM/Matheson; Halimelby; Bartholomew; Pat; Yuh	10226,459 08/23/02	
FA	70893	TW	MSS MBG	DESIGN FOR A LINEAR INJECTOR ASSEMBLY/Matheson; Halimelby; Bartholomew; Pat; Yuh	PI20023124 08/23/02	Malaysia
FP	70893	PC	MSS	DESIGN FOR A LINEAR INJECTOR ASSEMBLY/Matheson; Halimelby; Bartholomew; Pat; Yuh	91119174 08/23/02	Taiwan
P	70896		MSS	PROTECTIVE SHIELD AND SYSTEM FOR GAS DISTRIBUTION/Matheson; Halimelby; Bartholomew; Pat; Yuh	PCT/US02/27376 08/26/02	PCT
A	70896		MSS	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bartolomew; Bailey; Pat; Yuh	60314,760 08/24/01	Closed
I-71935/MESS (463035-826)	1089123			10226,773 08/23/02		

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
PA 70896 MY	MSS MBG	CONTROL SYSTEM AND METHOD/Bailey; Pat; Yuh	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bailey; Pat; Yuh	PI20023123 08/23/02		Malaysia
FA 70896 TW	MSS MBG	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bailey; Pat; Yuh	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bailey; Pat; Yuh	91119175 08/23/02		Taiwan
FP 70896 PC	MSS	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bailey; Pat; Yuh	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bailey; Pat; Yuh	PC1030277372 08/26/02	PCT	
P 71033	MSS	APPARATUS AND PROCESS FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	APPARATUS AND PROCESS FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	60332397 11/16/01	Closed	
A 71033	MSS	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	10/10/6/07 03/25/02		China
FA 71033 CN	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	02157380.0 11/15/02		Japan
FA 71033 JP	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	2002-333209 11/18/02		South Korea
FA 71033 KR	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	2002-0071019 11/15/02		Malaysia
FA 71033 SG	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	FI20024197 11/11/02		Singapore
FA 71033 TW	MSS	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	200206876-5 11/14/02		Taiwan
PH. 71033 EP	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzak; Hering; Helms; Osborne	91132057 11/11/02		Europe
				02257338.9 11/13/02		

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1039128

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 71033 1	MSS	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS; Sennati; Hering; Heine; Ohno	Closed			
A 71090	MSS	OPTIMIZATION OF CHEMICAL REACTION RATE COEFFICIENTS BY AUTOMATED ITERATIVE COMPUTER SIMULATIONS AND COEFFICIENT VARIATION USING A DESIGNED-EXPERIMENT APPROACH; Chaham; Bailey	Closed			
P 71181	MSS	HEATED VACUUM SUPPORT APPARATUS; Tom Kane, Jeff Bailey, Sam Kuris, Kris Veek	60/333,447 11/26/01	Closed		
A 71181	MSS TH	HEATED VACUUM SUPPORT APPARATUS; Kane, Bailey; Kuris; Veek	10/303,035 11/22/02			
FA 71181 MY	MSS	HEATED VACUUM SUPPORT APPARATUS; Kane, Bailey, Kuris, Veek	PI 20024390 11/25/02			Malaysia
FA 71181 TW	MSS	HEATED VACUUM SUPPORT APPARATUS; Kane, Bailey, Kuris; Veek	91134187 11/25/02			Taiwan
EP 71181 PC	MSS	HEATED VACUUM SUPPORT APPARATUS; Kane, Bailey; Kuris; Veek	PI 7032/38106 11/25/02			PCT
P 71197	MSS	IN-SITU THERMAL CHAMBER CLEANING/HEATING; Sennati; Sennati	60/379,381.. 05/08/02	Closed		
A 71197	MSS TH	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD; Hering; Sison; Sennati	10/318,664 12/12/02			
FA 71197 MY	MSS	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD; Hering; Sison; Sennati	PI 20031610 04/29/03			Malaysia
FA 71197 TW	MSS	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD; Hering; Sison; Sennati	92110202 04/30/03			Taiwan
PA 71197 PC	MSS	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD; Sennati	N/A			
A 71355	MSS	SEMICONDUCTOR WAFER CARRIER TRANSPORT APPARATUS; Sennati; Sander; Goldman; Mello	06/863,961 05/16/06	4,722,659 02/02/83	PCT	

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1059128

Reference No.			Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	71336	MSS	SEMICONDUCTOR WAFER CARRIER INPUT/OUTPUT DRAWER/Hoy III; Goldman; Mello	06/863,980 05/16/86	4,934,767 06/19/90	Abandoned
P	71514	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION TO ACHIEVE A COMPLETE GAP-FILL SUB-MICRON STRUCTURES/ Park; Bartholomew; Yuh	60/332,780 05/21/02	Closed	Abandoned
A	71514	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/Park; Bartholomew; Yuh	10/442,423 05/20/03		
FA	71514	MY	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/Park; Bartholomew; Yuh	FI 20031855 05/20/03		Malaysia
FA	71514	TW	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/Park; Bartholomew; Yuh	05/20/03		Taiwan
FP	71514	PC	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/Park; Bartholomew; Yuh	05/20/03		PCI
P	71564	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nezam; Rafiq; Chatterji	60/387,185 06/06/02	Closed	
A	71564	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nezam; Rafiq; Chatterji	104,56,850 06/06/03		
FA	71564	MY	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nezam; Rafiq; Chatterji	06/06/03		Malaysia
FA	71564	TW	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nezam; Rafiq; Chatterji	06/06/03		Taiwan

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169128

Reference No.	Title/Inventors				Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries	
	FP	71564	PC	MSS				
P	71581	MSS			OZONE OXIDATION OF SILICON SUBSTRATES FOR HIGH+ GATE STACKS/Senzaiti; Haining	60/399,463 07/29/02	Closed	PCT
A	71581	MSS			OZONE OXIDATION OF SILICON SUBSTRATES FOR HIGH+ GATE STACKS/Senzaiti; Haining			Unfiled
FP	71581	PC	MSS		OZONE OXIDATION OF SILICON SUBSTRATES FOR HIGH+ GATE STACKS/Senzaiti; Haining			PCT
FA	71581	TW	MSS		OZONE OXIDATION OF SILICON SUBSTRATES FOR HIGH+ GATE STACKS/Senzaiti; Haining	07/29/03		Taiwan
P	71582	MSS	WEN		OPTIMIZED MINI-BATCH CONFIGURABLE VERTICAL CHAMBER/Qu; Widman; Collier; Kowalik; Edwards; DuBois; Nam; Toraman; Mr; Stemer	60/396,536 07/15/02	Closed	PCT
P	71582	1	MSS	WEN	OPTIMIZED MINI-BATCH CONFIGURABLE VERTICAL CHAMBER/Qu; Widman; Collier; Kowalik; Edwards; DuBois; Nam; Toraman; Mr; Stemer	60/428,526 11/22/02	Closed	
P	71606	MSS	TH		SYSTEM AND METHOD FOR ATOMIC LAYER DEPOSITION AND REMOVAL/Kapkin; Sang-In Lee	60/391,011 06/23/02	Closed	
A	71606	MSS	TH		METHOD AND SYSTEM FOR ATOMIC LAYER DEPOSITION/Kapkin; Sang-In Lee			
FA	71606	TW	MSS		SYSTEM AND METHOD FOR ATOMIC LAYER DEPOSITION AND REMOVAL/Kapkin; Sang-In Lee			
FP	71606	PC	MSS		SYSTEM AND METHOD FOR ATOMIC LAYER DEPOSITION AND REMOVAL/Kapkin; Sang-In Lee	06/23/03		Taiwan
P	71606	1	MSS		METHOD AND SYSTEM FOR PHOTO-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL/Hahn; Jr; Kapkin; Sang-In Lee; Scandia	PCT/US03/19982 06/23/03 60/391,012 06/23/02	Closed	PCT

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1089128

Reference No.		Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	71606	I-TW MSS	METHOD AND SYSTEM FOR PHOTO-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL / Helme, K.; Kaplin; Sang-In Lee; Sennaki	06/23/03	Taiwan
PP	71606	I-PC MSS	METHOD AND SYSTEM FOR PHOTO-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL / Helme, K.; Kaplin; Sang-In Lee; Sennaki	06/23/03	PCT
P	71622	MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS/Sennaki; Sang-In Lee	60397,029 07/18/02	Closed
A	71622	MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS/Sennaki; Sang-In Lee		
FA	71622	TW MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS/Sennaki; Sang-In Lee		Taiwan
PP	71622	PC MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS/Sennaki; Sang-In Lee	07/16/03	PCT
P	71637	MSS	AFNEKT MACH 2 WAFER HEATING & TRANSLATE SYSTEM & DESIGN/DeDomyen	92119581 07/17/03	Closed
P	71638	MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS/Sennaki; Sang-In Lee	60396,735 07/19/02	Closed
A	71638	MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS/Sennaki; Sang-In Lee	60396,723 07/19/02	Closed
FA	71638	TW MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS/Sennaki; Sang-In Lee		Taiwan
PP	71638	PC MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS/Sennaki; Sang-In Lee	07/17/03	PCT
P	71639	MSS	LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS/Sennaki; Sang-In Lee	07/19/02	Closed
FA	71639	TW MSS	LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS/Sennaki; Sang-In Lee	07/17/03	Taiwan
PP	71639	PCT MSS	LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS/Sennaki; Sang-In Lee	07/16/03	PCT

F-71635MSS (463035-828)
1059128

Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	71640	MSS	LOW TEMPERATURE DIELECTRIC DEPOSITION USING AMINOSILANE AND OZONE/Senzaki	60/396,746 07/19/02	Closed	
FA	71640	TW	MSS	LOW TEMPERATURE DIELECTRIC DEPOSITION USING AMINOSILANE AND OZONE/Senzaki	07/17/03	Taiwan
PP	71640	PC	MSS	LOW TEMPERATURE DIELECTRIC DEPOSITION USING AMINOSILANE AND OZONE/Senzaki	07/17/03	PCT
P	71641	MSS	MOCVD & ATOMIC LAYER DEPOSITION OF HF-O-N & HF-SI-O-N FOR GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee	60/396,744 07/19/02	Closed	
A	71641	MSS	MOCVD & ATOMIC LAYER DEPOSITION OF HF-O-N & HF-SI-O-N FOR GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee			
FA	71641	TW	MSS	MOCVD & ATOMIC LAYER DEPOSITION OF HF-O-N & HF-SI-O-N FOR GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee	92119583 07/17/03	Taiwan
PP	71641	PC	MSS	MOCVD & ATOMIC LAYER DEPOSITION OF HF-O-N & HF-SI-O-N FOR GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee	07/17/03	PCT
P	71642	MSS	VACUUM UV ASSISTED ATOMIC LAYER DEPOSITION/Senzaki; Sang-In Lee	60/396,743 07/19/02	Closed, combined with 71606-1	
P	71643	MSS	STEAM OXIDATION FOR THE FORMATION OF THIN GATE AND CAPACITOR DIELECTRIC WITH IMPROVED ELECTRICAL PROPERTIES/Senzaki; Biehler; Haining	60/396,733 07/19/02	Closed	
FA	71643	TW	MSS	STEAM OXIDATION FOR THE FORMATION OF THIN GATE AND CAPACITOR DIELECTRIC WITH IMPROVED ELECTRICAL PROPERTIES/Senzaki; Biehler; Haining	07/17/03	Taiwan
PP	71643	PC	MSS	STEAM OXIDATION FOR THE FORMATION OF THIN GATE AND CAPACITOR DIELECTRIC WITH IMPROVED ELECTRICAL PROPERTIES/Senzaki; Biehler; Haining	07/17/03	PCT

I-71632/MSS (463635-828)
1059728

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P 71644	MSS	IN-SITU FORMATION OF MM CAPACITORS/Sang-In Lee		60/396,734 07/19/02	Closed	
PA 71644 TW	MSS	IN-SITU FORMATION OF MM CAPACITORS/Sang-In Lee				
FP 71644 PC	MSS	IN-SITU FORMATION OF MM CAPACITORS/Sang-In Lee		07/17/03		Taiwan
P 71645	MSS	ATOMIC LAYER DEPOSITION FOR CAPACITOR APPLICATIONS/Sang-In Lee		07/17/03		PCT
A 71645	MSS	ATOMIC LAYER DEPOSITION FOR CAPACITOR APPLICATIONS/Sang-In Lee		60/396,745 07/19/02	Closed, combined with 71638	
P 71653	MSS	METHOD OF MAKING METAL CAPS FOR SEMICONDUCTOR DEVICES/Kaplin		60/397,031 07/18/02	Closed	
A 71653	MSS	METHOD OF MAKING METAL CAPS FOR SEMICONDUCTOR DEVICES/Kaplin		N/A		
P 71720	MSS	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki		60/404,372 08/18/02	Closed	
A 71720	MSS	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki				
PA 71720 TW	MSS	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki		08/14/03		Taiwan
FP 71720 PC	MSS	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki		08/18/03		PCT
P 71721	MSS	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki		60/404,371 08/18/02	Closed	

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
	App.	Patent No.	Date			
A 71721	MSS	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS	Sang-In Lee; S.K. Lee; Shin; Sonzaki			
PA 71721	TW	MSS	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS	Sang-In Lee; S.K. Lee; Shin; Sonzaki	08/14/03	Taiwan
EP 71721	PC	MSS	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS	Sang-In Lee; S.K. Lee; Shin; Sonzaki	08/18/03	PCT
P 71722		MSS	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE	Sang-In Lee; S.K. Lee; Shin; Sonzaki	604404-363 08/18/02	Closed
A 71722	MSS	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE	Sang-In Lee; S.K. Lee; Shin; Sonzaki			
PA 71722	TW	MSS	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE	Sang-In Lee; S.K. Lee; Shin; Sonzaki	08/14/03	Taiwan
EP 71722	PC	MSS	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE	Sang-In Lee; S.K. Lee; Shin; Sonzaki	08/18/03	PCT
P 71730		MSS	LOW TEMPERATURE DEPOSITION OF SILICON BASED THIN FILMS BY SINGLE WALL RAPID THERMAL CHEMICAL VAPOR DEPOSITION (RTCVD)	Sanzaki; Basell; Teesdale; Sang-In Lee; S.K. Lee; Shin; Sonzaki	604408-709 09/05/02	Closed
A 71730	MSS	LOW TEMPERATURE DEPOSITION OF SILICON BASED THIN FILMS BY SINGLE WALL RAPID THERMAL CHEMICAL VAPOR DEPOSITION (RTCVD)	Sanzaki; Basell; Teesdale; Sang-In Lee; S.K. Lee; Shin; Sonzaki	09/05/03		
P 71730	I	MSS	LOW TEMPERATURE DEPOSITION OF SILICON BASED THIN FILMS BY SINGLE WALL RAPID THERMAL CHEMICAL VAPOR DEPOSITION (RTCVD)	Sanzaki; Basell; Teesdale; Sang-In Lee; S.K. Lee; Shin; Sonzaki	Closed, combined with 71730	

I-719360A5 (463085-828)
1089128

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P 71731	MSS TH	SEQUENTIAL TWO-STEP ATOMIC LAYER DEPOSITION OF COPPER SEED LAYER/Senzaki		60419,633 10/17/02		
A 71731	MSS	SEQUENTIAL TWO-STEP ATOMIC LAYER DEPOSITION OF COPPER SEED LAYER/Senzaki				Client Ref # D-7006
A 71732	MSS	TWO-STEP SEQUENTIAL GROWTH OF HIGH-K GATE DIELECTRICS BY ATOMIC LAYER DEPOSITION/Senzaki				Client Ref # D-7005
A 71733	MSS TH	ANNEAL PROCESS FOR SILICON NITRIDE DIELECTRIC THIN FILM/Senzaki; Bitoiko				Client Ref # D-7007
A 71748	MSS WEN	THERMAL PROCESSING SYSTEM AND CONFIGURABLE VERTICAL CHAMBER/DuBois; Name				
FA 71748 TW	MSS	THERMAL PROCESSING SYSTEM AND CONFIGURABLE VERTICAL CHAMBER/DuBois; Name: Wildman; Qui; Kowald				Taiwan
FP 71748	PC	MSS THERMAL PROCESSING SYSTEM AND CONFIGURABLE VERTICAL CHAMBER/DuBois; Name: Wildman; Qui; Kowald		07/10/03		PCT
A 71749	MSS TH	PEDESTAL THERMAL SHIELD/Wildman; Qui		07/10/03		
A 71750	MSS TH	TERMAL PROCESSING APPARATUS AND METHOD OF BACKFILING A CHAMBER CLEANING/Tetteman		Closed, combined with 71748		
FA 71750 TW	MSS	TERMAL PROCESSING APPARATUS AND METHOD OF BACKFILING A CHAMBER CLEANING/Tetteman				Taiwan
FP 71750 CT	MSS	TERMAL PROCESSING APPARATUS AND METHOD OF BACKFILING A CHAMBER CLEANING/Tetteman		07/10/03		PCT
A 71751	MSS TH	VACUUM ASSEMBLY WITH MULTI-STAGE VALVE SEQUENCE/Qui		07/10/03		

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
PA 71751 TW MSS	VACUUM ASSEMBLY WITH MULTI-STAGE VALVE SEQUENCE; Qui			07/10/03		Taiwan
PP 71751 PC MSS	VACUUM ASSEMBLY WITH MULTI-STAGE VALVE SEQUENCE; Qui			07/10/03		PCT
A 71752	MSS	WEN	CYCLONIC COOLING SYSTEM AND METHOD; Qui; Collins			
PA 71752 TW MSS	CYCLONIC COOLING SYSTEM AND METHOD; Qui; Collins					Taiwan
PP 71752 PC MSS	CYCLONIC COOLING SYSTEM AND METHOD; Qui; Collins			07/10/03		PCT
A 71753	MSS	WEN	COOLING SYSTEM AND METHOD; Qui; Collins	07/10/03		
A 71754	MSS		FEED FORWARD TEMPERATURE CONTROLLER; Ma	Closed, combined with 71752		
A 71755	MSS	KRG	ALIGNMENT APPARATUS AND METHOD OF ALIGNING A WAFER; Ma	on hold		
A 71756	MSS		COMMUNICATION PROTOCOL AND METHOD OF IMPROVED ROBOT THROUGHPUT; Ma			
A 71757	MSS		DISTRIBUTED SINGLE WIRE NETWORKING ELEVATOR CONTROL SYSTEM AND METHOD; Ma			
PA 71757 TW MSS	SERVOMOTOR CONTROL SYSTEM & METHOD IN A SEMICONDUCTOR MANUFACTURING ENVIRONMENT; John Ma			07/10/03		Taiwan
PP 71757 PC MSS	SERVOMOTOR CONTROL SYSTEM & METHOD IN A SEMICONDUCTOR MANUFACTURING ENVIRONMENT; John Ma			07/10/03		PCT
A 71758	MSS	KRG	LOAD PORT; Jeffrey E. Kowald			
PA 71758 TW MSS	LOAD PORT APPARATUS; Jeffrey E. Kowald			07/15/03		Taiwan

I-71935/MSS (463035-828)
1099128

Reference No.	Title/Inventors			Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FP 71758 PC MSS	LOAD PORT APPARATUS; Jeffrey R. Kowalski			07/15/03		PCT
A 71759	MSS	THE THERMAL PROCESSING CHAMBER ENVIRONMENTAL CONTROL SYSTEM AND METHOD; Alan Stauffer				
PA 71759 TW	MSS	CONTROL OF A GASEOUS ENVIRONMENT IN A WAFER LOADING CHAMBER; Alan Stauffer		07/15/03		Taiwan
FP 71759 PC MSS	CONTROL OF A GASEOUS ENVIRONMENT IN A WAFER LOADING CHAMBER; Alan Stauffer			07/15/03		PCT
A 71768	MSS WEN	METHOD AND SYSTEM FOR ISOTHERMAL HEATING OF WAFERS; Jeffrey Kowalski	Closed, combined with 71748			
A 71795	MSS	HEATER ELEMENT SELECTABLE FOR VARIABLE TEMPERATURE PROCESSING/G/Qin				
PA 71795 TW	MSS	VARIABLE HEATER ELEMENT FOR LOW TO HIGH TEMPERATURE RANGES/Qin		07/10/03		Taiwan
FP 71795 PC MSS	VARIABLE HEATER ELEMENT FOR LOW TO HIGH TEMPERATURE RANGES/Qin			07/10/03		PCT
A 71796	MSS	T-RAIL SUPPORT/DuBois				
PA 71796 TW	MSS	METHOD & APPARATUS FOR SUPPORTING SEMICONDUCTOR WAFERS/DuBois		07/10/03		Taiwan
FP 71796 PC MSS	METHOD & APPARATUS FOR SUPPORTING SEMICONDUCTOR WAFERS/DuBois			07/10/03		PCT
A 71797	MSS	FEED FORWARD CONTROL SYSTEM AND METHOD/Tschamm; Radiff (This case may be related to A-71734)				
A 71798	MSS	SYSTEM ARCHITECTURE AND METHOD FOR SEMICONDUCTOR FABRICATION/Helmut Wheen				

Reference No.		Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	71824	MSS TH Lopata	REMOTE PLASMA NITRIDATION OF HIGH-K GATE DIELECTRICS/Suzuki; Berew, Chashan; Higuchi; Lopata	60424,891 11/02/02	
A	71824	MSS	REMOTE PLASMA NITRIDATION OF HIGH-K GATE DIELECTRICS/Suzuki; Berew, Chashan; Higuchi; Lopata		
A	71884	MSS TH	METHOD OF ATOMIC LAYER REMOVAL OR HI-RACING/Song-in Lee	Closed, combined with 71606	
P	72081	MSS	TRANSPORT SYSTEM HAVING SHARED LOAD, LOCK FRONT-END ASSEMBLY FOR TRANSFER OF MEDIA IN A CONTROLLED ENVIRONMENT	60/443,969 01/31/03	
P	72138	MSS	ELECTRODE STRUCTURE AND METHOD OF FABRICATING AN ELECTRODE HAVING LOW TEMPERATURE OXIDE FILM; S.I. Lee, Y. Suzuki		
P	72218	MSS	METHOD OF FABRICATING MULTI-COMPONENT FILMS; Y. Suzuki, S.G. Park	60/464,458 04/21/03	Client Ref. No. - D-7031
P	72214	MSS	DELIVERY SYSTEM FOR DELIVERY MANIFOLD; DeDominicis, Neri	60/473,379 05/29/03	Client Ref. No. - D-2493
A	72332	MSS	IN-SITE CLEANING OF COPPER DETECTION CHAMBER & PARTS		
A	72333	MSS	METHOD OF REDUCING CONTACT RESISTANCE OF COPPER INTERCONNECT		
A	72344	MSS	BATCH FURNACE WAFER RADIAL DELTA TEMPERATURE CONTROL USING A BOTTOM AND TOP HEATER		
A	72345	MSS	SEMICONDUCTOR VERTICAL FURNACE HALO RING CONCEPT; D. DuBois, C. Pomer, M. Mogard		

Reference No.	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries

Reference No.

"A" denotes US a patent/patent application/invention disclosure
 "TA" "FP" and "TF" denote a foreign patent/patent application